

MILITARY SPECIFICATION

MICROCIRCUIT, DIGITAL, 4096-BIT SCHOTTKY, BIPOLAR, PROGRAMMABLE READ-ONLY MEMORY (PROM),
MONOLITHIC SILICON

Inactive for new design after 24 July 1995
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This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product herein shall consist of this specification sheet and MIL-PRF 38535.

1. SCOPE

1.1 Scope. This specification covers the detail requirements for monolithic silicon, programmable read-only memory (PROM) microcircuits which employ thin film nichrome (NiCr) resistors, titanium-tungsten (TiW), or zapped vertical emitter (ZVE) as the fusible link or programming element. Two product assurance classes and a choice of case outlines and lead finishes are provided and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.4).

1.2 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-38535, and as specified herein.

1.2.1 Device types. The device types are as follows:

<u>Device type</u>	<u>Circuit</u>
01	512 word/8 bits per word PROM with uncommitted collector
02	512 word/8 bits per word PROM with active pull-up and a choice third high-impedance state output
03	512 word/8 bits per word PROM with active pull-up and a third high-impedance state output
04	512 word/8 bits per word PROM with uncommitted collector
05	512 word/8 bits per word PROM with active pull-up and a third high-impedance state output

1.2.2 Device class. The device class is the product assurance level as defined in MIL-PRF-38535.

1.2.3 Case outlines. The case outlines are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
J	GDIP1-T24 or CDIP2-T24	24	Dual-in-line
K	GDFP2-F24 or CDFP3-F24	24	Flat pack
X	See figure 1	24	Flat pack
Y	See figure 2	20	Dual-in-line
Z	CQCC1-N24	24	Square leadless chip carrier

Comments, suggestions, or questions on this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DLA LAND AND MARITIME-VAS, P. O. Box 3990, Columbus, OH 43218-3990, or emailed to Memory@dla.mil . Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at https://assist.dla.mil
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AMSC N/A

FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range	-0.5 V dc to +7.0 V dc
Input voltage range	-1.5 V dc at -10 mA to +5.5 V dc
Storage temperature range	-65° to +150°C
Lead temperature (soldering, 10 seconds).....	+300°C
Thermal resistance, junction to case (θ_{JC}) <u>1/</u> :	
Cases J, K, and Y	30°C/W
Case X and Z	36° C/W
Output voltage applied	-0.5 V dc dc to +V _{CC}
Output sink current.....	100 mA
Maximum power dissipation (P _D) <u>2/</u>	1.02 W
Maximum, junction temperature (T _J)	+175°C

1.4 Recommended operating conditions.

Supply voltage	+4.5 V dc minimum to +5.5 V dc maximum
Minimum high-level input voltage	2.0 V dc
Maximum low-level input voltage	0.8 V dc
Normalized fanout (each output)	8 mA <u>3/</u>
Case operating temperature range (T _C)	-55 °C to +125 °C

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications and Standards. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard for Microelectronics.
MIL-STD-1835 - Interface Standard Electronic Component Case Outline

(Copies of these documents are available online at <http://quicksearch.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein (except for related specification sheets), the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

1/ Heat sinking is recommended to reduce the junction temperature.

2/ Must withstand the added P_D due to short circuit test (e.g. I_{OS}).

3/ 16 mA for circuit F devices.

3. REQUIREMENTS

3.1 Qualification. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.3).

3.2 Item requirements. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.3 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.

3.3.1 Terminal connections. The terminal connections shall be as specified on figures 3.

3.3.2 Truth table

3.3.2.1 Unprogrammed devices. The truth table for unprogrammed devices for contracts involving no altered item drawing shall be as specified on figure 4. When required in groups A, B, or C (see 4.4), the devices shall be programmed by the manufacturer prior to test in a checkerboard pattern (a minimum of 50 percent of the total number of bits programmed) or to any altered item drawing pattern which includes at least 25 percent of the total number of bits programmed.

3.3.2.2 Programmed devices. The truth table for programmed devices shall be as specified by the altered item drawing.

3.3.3 Logic diagram. The logic diagram shall be as specified on figure 5.

3.3.4 Case outlines. The case outlines shall be as specified in 1.2.3.

3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).

3.5 Electrical performance characteristics. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.

3.6 Electrical test requirements. The electrical test requirements shall be as specified in table II, and where applicable, the altered item drawing. The electrical tests for each subgroup are described in table III.

3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.

3.8 Processing options. Since the PROM is an unprogrammed memory capable of being programmed by either the manufacturer or the user to result in a wide variety of configurations, two processing options are provided for selection in the contract, using an altered item drawing.

3.8.1 Unprogrammed PROM delivered to the user. All testing shall be verified through group A testing as defined in 3.3.2.1, table II, and table III. It is recommended that users perform subgroups 7 and 9 after programming to verify the specific program configuration.

3.8.2 Manufacturer-programmed PROM delivered to the user. All testing requirements and quality assurance provisions herein, including the requirements of the altered item drawing, shall be satisfied by the manufacturer prior to delivery.

3.9 Microcircuit group assignment. The devices covered by this specification shall be in microcircuit group number 14 (see Appendix A MIL-PRF-38535.)

TABLE I. Electrical performance characteristics.

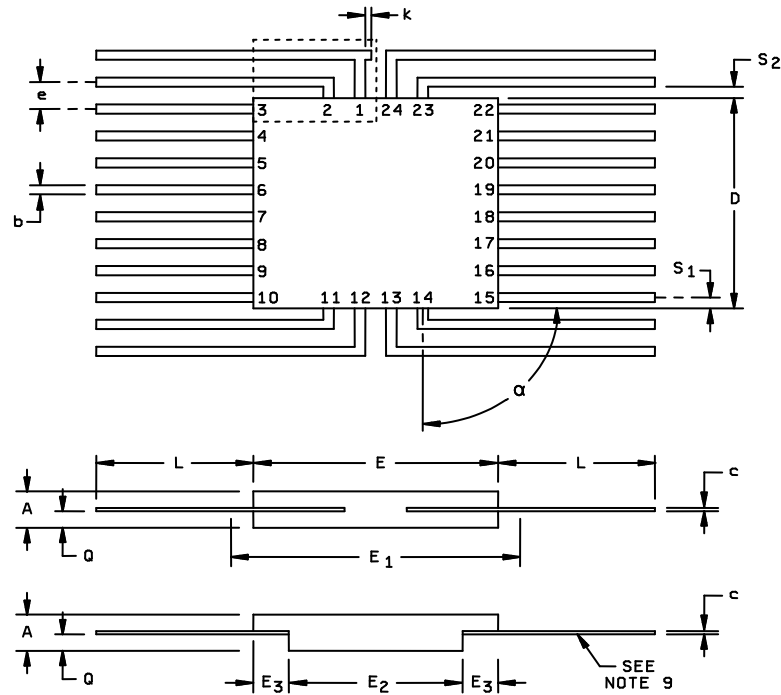
Test	Symbol	Conditions 1/ 2/	Device type	Limits		Unit
				Min	Max	
High-level output voltage	V _{OH}	V _{CC} = 4.5 V, I _{OH} = -2 mA	02,03,05	2.4	---	V
Low-level output voltage	V _{OL}	V _{CC} = 4.5 V, I _{OL} = 8 mA 3/	All	---	0.5	V
Input clamp voltage	V _{IC}	V _{CC} = 4.5 V, I _{IN} = -10 mA, T _C = 25°C	All	---	-1.5	V
Maximum collector cut-off current	I _{CEX}	V _{CC} = 5.5 V, V _O = 5.2 V	01,04	---	100	μA
High-impedance (off-state) output high current	I _{OHZ}	V _{CC} = 5.5 V V _O = 5.2 V	02,03,05	---	100	μA
High-impedance (off-state) output low current	I _{OLZ}	V _{CC} = 5.5 V, V _O = 0.5 V	02,03,05		-100	μA
High-level input current	I _{IH1}	V _{CC} = 5.5 V, V _{IN} = 5.5 V	All	---	50	μA
	I _{IH2}	V _{CC} = 5.5 V, V _{IN} = 4.5 V, special program- ming pin	All	---	100	μA
Low-level input current	I _{IL1}	V _{CC} = 5.5 V, V _{IN} = 0.5 V	All	-1.0	-250	μA
	I _{IL2}	V _{CC} = 5.5 V, V _{IN} = 0.5 V, for CE ₃ and CE ₄	01,02	-1.0	-1000	μA
Short circuit output current	I _{OS}	V _{CC} = 5.5 V, V _O = 0.0 V 4/	02,03,05	-10	-100	mA
Supply current	I _{CC}	V _{CC} = 5.5 V, V _{IN} = 0, out- puts = open	01,02,03	---	185	mA
			04,05	---	155	mA
Propagation delay time, high-to-low level logic, address to output	t _{PHL1}	V _{CC} = 4.5 V and 5.5 V, C _L = 30 pF (see figure 6)	01,02,03	---	90	ns
			04,05	---	80	ns
Propagation delay time, low-to-high level logic, address to output	t _{PLH1}		01,02,03	---	90	ns
			04,05	---	80	ns
Propagation delay time, high-to-low level logic, enable to output	t _{PHL2}		01,02,03	---	50	ns
			04,05	---	40	ns
Propagation delay time, low-to-high level logic, enable to output	t _{PLH2}		01,02,03	---	50	ns
			04,05		40	ns

1/ Complete terminal conditions shall be as specified on table III.

2/ For device type 03, the fusing pins FE_1 and FE_2 may be grounded or floating during operation.

3/ $I_{OL} = 16 \text{ mA}$ for circuit F devices.

4/ Not more than one output shall be grounded at one time. Output shall be at high logic level prior to test.



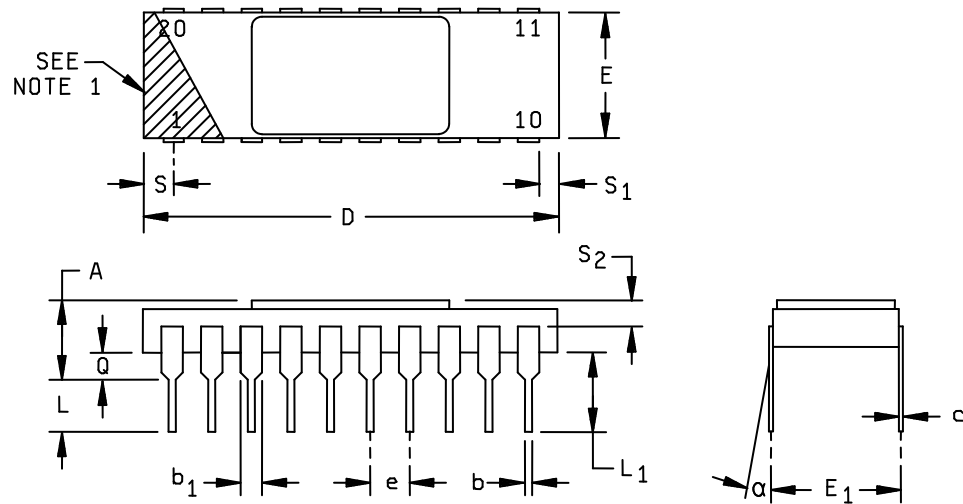
Dimension					
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
A	.045	.090	1.14	2.29	
b	.015	.019	.38	.48	5
c	.003	.006	.08	.15	5
D	----	.400	----	10.16	3
E	.340	.385	8.64	9.78	
E ₁	----	.400	----	10.16	3
E ₂	.125	----	3.18	----	
E ₃	.030	----	.76	----	14
e	.050 BSC		1.27 BSC		4, 6
k	.008	.015	.20	.38	10
L	.250	.370	6.35	9.40	
Q	.010	.040	.25	1.02	2
S ₁	.005	----	.13	----	7, 8
S ₂	.005	---	.13	----	11
α	30°	90°	30°	90°	12, 13

FIGURE 1. Case outline X.

NOTES:

1. Index area; a notch or a pin one identification mark shall be located adjacent to pin one and shall be within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab (dimension k) may be used to identify pin one.
2. Dimension Q shall be measured at the point of exit of the lead from the body.
3. This dimension allows for off-center lid, meniscus and glass overrun.
4. The basic pin spacing is .050 (1.25 mm) between centerlines. Each pin centerline shall be located within $\pm .005$ (0.13 mm) of its exact longitudinal position relative to pins relative to pins 1 and 24.
5. All leads – increase maximum limit by .003 (0.08mm) measured at the center of the flat, when lead finish A is applied.
6. Twenty-two spaces.
7. Applies to all four corners (leads number 3, 10, 15, and 22).
8. Dimension S_1 may be .000 (0.00 mm) if leads number 3, 10, 15, and 22 bend toward the cavity of the package within one lead width from the point of entry of the lead, into the body or if the leads are brazed to the metallized ceramic body (see MIL-STD-1835) .
9. Optional configuration: if this configuration is used, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
10. Optional, see note 1. If a pin one identification mark is used in addition to this tab, the minimum limit of dimension k does not apply.
11. Applies to leads number 2, 11, 14, and 23.
12. Lead configuration is optional within dimension E except dimensions b and c apply (see MIL-STD-1835).
13. Applies to lead numbers 1, 2, 11, 12, 13, 14, 23, and 24.
14. Applies to all edges.

FIGURE 1. Case outline X – Continued.



Dimension					
Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
A	----	.175	----	4.44	
b	.016	.020	.41	.51	11, 8
b ₁	.040	.060	1.02	1.52	8, 2
C	.008	.012	.20	.30	11, 8
D	.970	1.010	24.64	25.65	4
E	.280	.300	7.11	7.62	4
E ₁	.290	.320	7.37	8.13	7
e	.090	.110	2.29	2.79	5, 9
L	.125	.180	3.18	4.58	
L ₁	.150	----	3.81	----	
Q	.020	.060	.51	1.52	3
S	----	.098	----	2.49	6
S ₁	.005	----	.13	----	6
S ₂	.005	----	.13	----	8
α	0°	15°	0°	15°	

FIGURE 2. Case outline Y.

NOTES:

1. Index area; a notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
2. The minimum limit for dimension b_1 may be .020 (.51 mm) for leads number 1, 10, 11, and 20 only.
3. Dimension Q shall be measured from the seating plane to the base plane.
4. This dimension allows for off-center lid, meniscus and glass overrun.
5. The basic pin spacing is .100 (2.54 mm) between centerlines. Each pin centerline shall be located within $\pm .010$ (.25 mm) of its exact longitudinal position relative to pins 1 and 20.
6. Applies to all four corners (leads number 1, 10, 11, and 20) (see MIL-STD-1835).
7. Lead center when α is 0° . E_1 shall be measured at the centerline of leads (see MIL-STD-1835).
8. All leads – Increase maximum limit by .003 (.08 mm) measured at the center of the flat, when lead finish A is applied.
9. Eighteen spaces.
10. No organic or polymeric materials shall be molded to the bottom of the package.
11. Applies to all leads.

FIGURE 2. Case outline Y – Continued.

Device type	01 and 02	03	04 and 05
Case outline	J, K, X, and Z	J, K, and X	Y
Terminal number	Terminal symbol		
1	A7	A3	A0
2	A6	A4	A1
3	A5	A5	A2
4	A4	A6	A3
5	A3	A7	A4
6	A2	A8	O1
7	A1	O1	O2
8	A0	O2	O3
9	O1	O3	O4
10	O2	O4	GND
11	O3	FE ₂	O5
12	GND	GND	O6
13	O4	FE ₁	O7
14	O5	O5	O8
15	O6	O6	CE ₁
16	O7	O7	A5
17	O8	O8	A6
18	CE ₄	STROBE	A7
19	CE ₃	CE ₂	A8
20	CE ₂	CE ₁	V _{CC}
21	CE ₁	A0	----
22	NC	A1	----
23	A8	A2	----
24	V _{CC}	V _{CC}	----

NOTE: Case Z: option A with active terminals on plane 1.

FIGURE 3. Terminal connections.

Device types 01 and 02

WORD NO.	ENABLE				ADDRESS										DATA							
	$\overline{\text{CE}}_1$	$\overline{\text{CE}}_2$	CE_3	CE_4	A_8	A_7	A_6	A_5	A_4	A_3	A_2	A_1	A_0	O_1	O_2	O_3	O_4	O_5	O_6	O_7	O_8	
NA	L	L	L	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	L	L	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	H	L	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	H	L	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	L	H	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	L	H	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	H	H	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	H	H	L	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	L	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	L	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	H	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	H	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	L	H	H	X	X	X	X	X	X	X	X	X	4/	4/	4/	4/	4/	4/	4/	4/	
NA	H	L	H	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	L	H	H	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	
NA	H	H	H	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC	

Device type 03

WORD NO.				ADDRESS									DATA							
	$\overline{\text{CE}}_1$	CE ₂	STROBE	A ₈	A ₇	A ₆	A ₅	A ₄	A ₃	A ₂	A ₁	A ₀	O ₁	O ₂	O ₃	O ₄	O ₅	O ₆	O ₇	O ₈
NA	L	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC
NA	H	L	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC
NA	L	H	H	X	X	X	X	X	X	X	X	X	4/	4/	4/	4/	4/	4/	4/	4/
NA	H	H	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC
NA	L	H	L	X	X	X	X	X	X	X	X	X	Last data is latched							

Device types 04 and 05

WORD NO.	ENABLE	ADDRESS									DATA							
	$\overline{\text{CE}}_1$	A ₈	A ₇	A ₆	A ₅	A ₄	A ₃	A ₂	A ₁	A ₀	O ₁	O ₂	O ₃	O ₄	O ₅	O ₆	O ₇	O ₈
NA	H	X	X	X	X	X	X	X	X	X	OC	OC	OC	OC	OC	OC	OC	OC
NA	L	X	X	X	X	X	X	X	X	X	4/	4/	4/	4/	4/	4/	4/	4/

NOTES:

1. NA = Not applicable.
2. X = Input may be high level, low level, or open circuit.
3. OC = Open circuit (high resistance output).
4. The outputs for an unprogrammed device shall be high for circuits A, B, D, and F, and low for circuit C, G and H.

FIGURE 4. Truth table (unprogrammed).

LOGIC CIRCUIT A
(Device types 01 and 02)

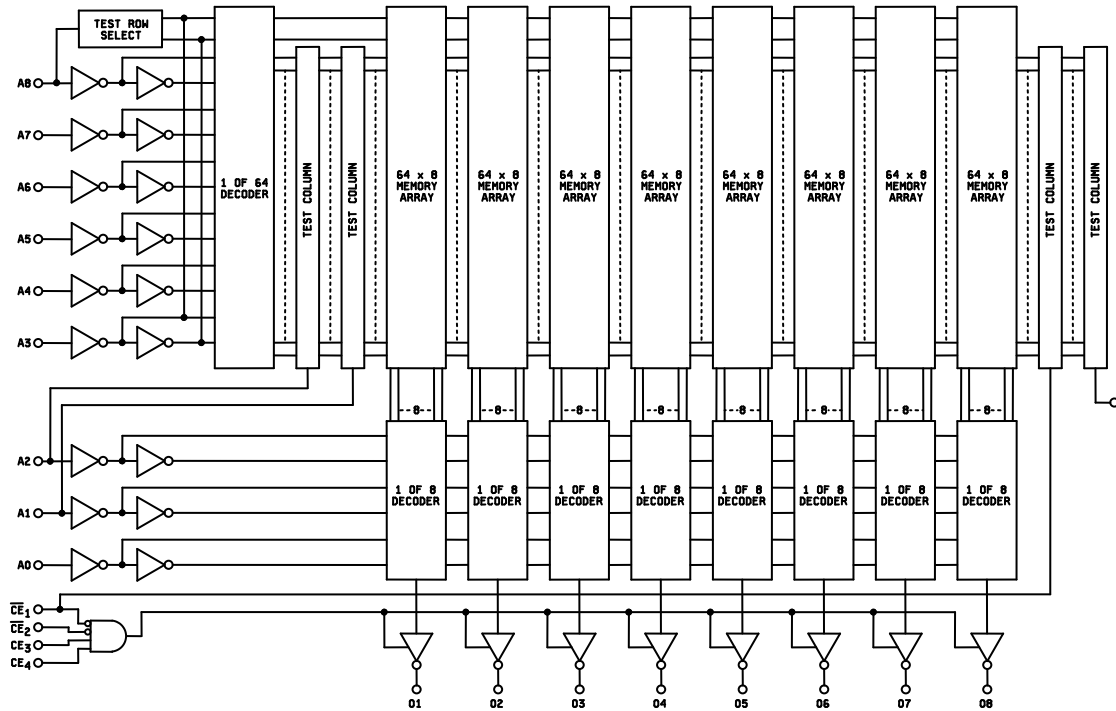
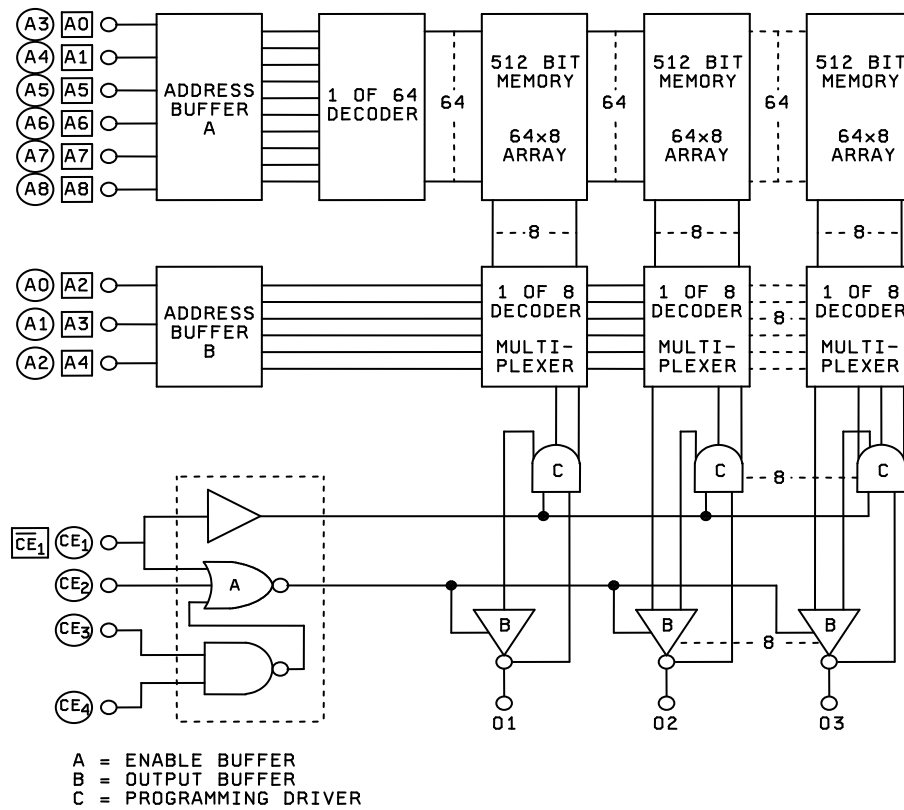


FIGURE 5. Logic diagrams.

LOGIC CIRCUIT B
(Device types 01, 02, 04, & 05) and
LOGIC CIRCUIT F
(Device type 05)

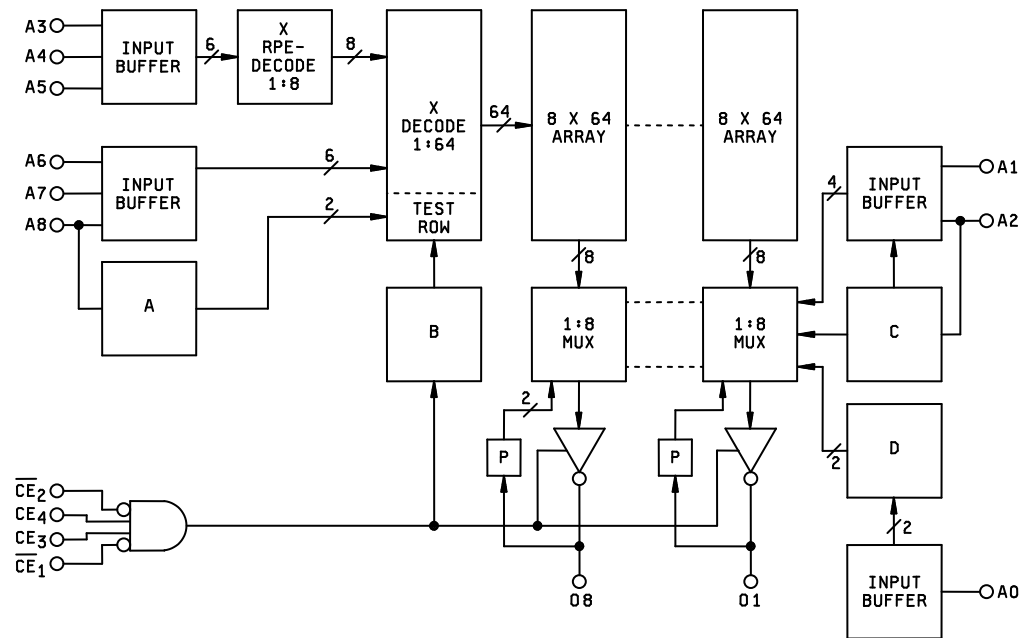


ADDRESS AND PIN DESIGNATIONS IN ○ REFER TO 01 AND 02

ADDRESS AND PIN DESIGNATIONS IN □ REFER TO 04 AND 05

FIGURE 5. Logic diagrams – Continued.

LOGIC CIRCUIT C
(Device types 01 and 02) and
LOGIC CIRCUIT H
(Device type 02)

FIGURE 5. Logic diagrams – Continued.

LOGIC CIRCUIT C
(Device type 03)

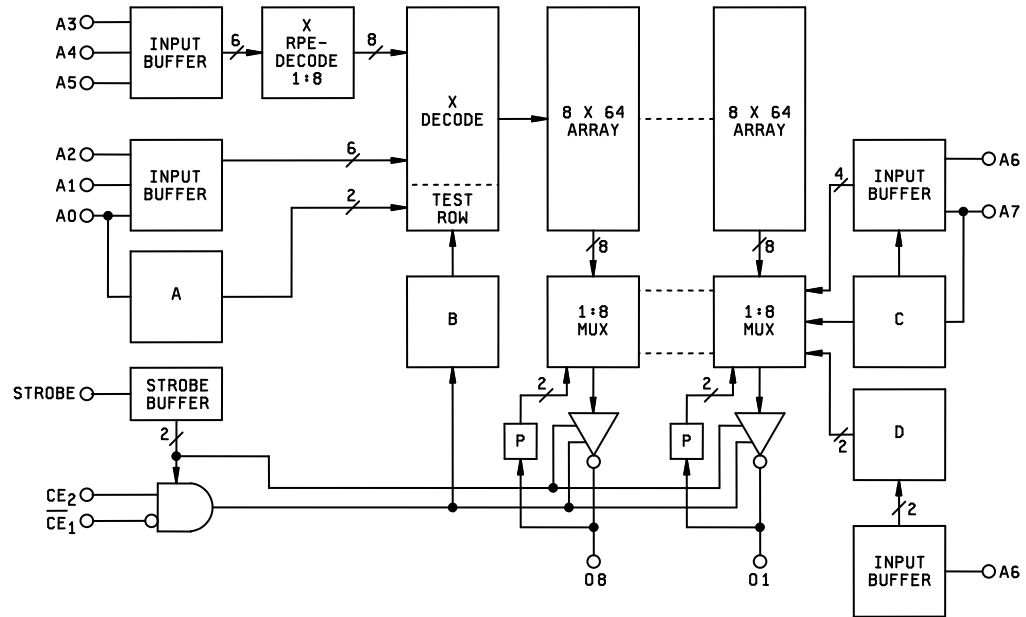
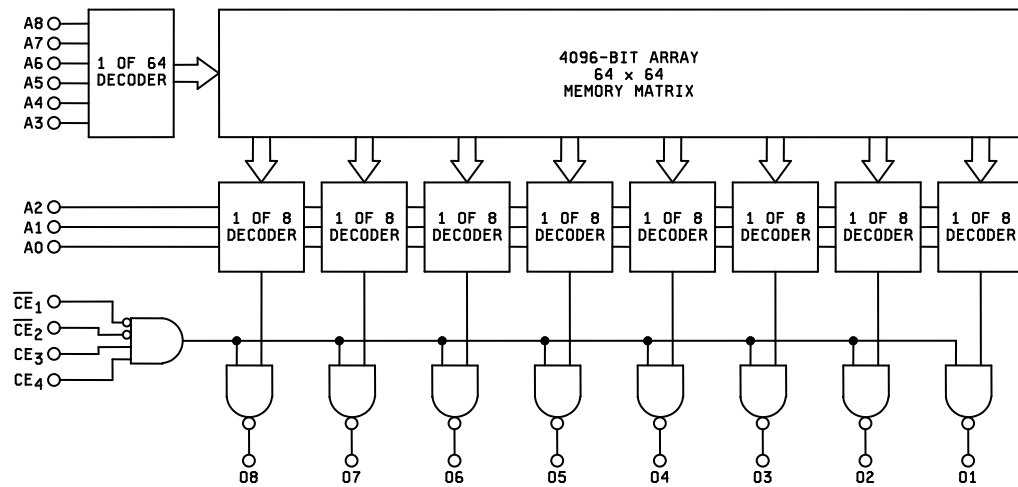


FIGURE 5. Logic diagrams – Continued.

LOGIC CIRCUIT D
(Device types 01 and 02)

FIGURE 5. Logic diagrams - Continued

LOGIC CIRCUIT G
(Device type 01)

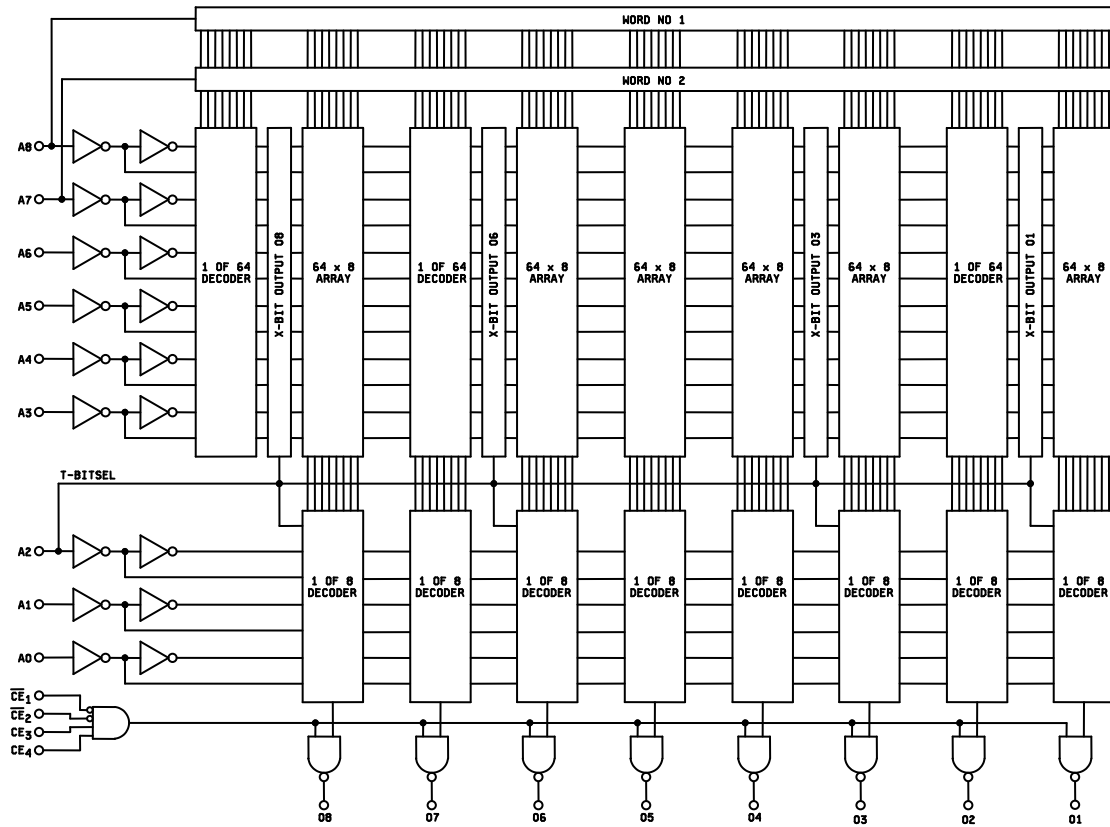
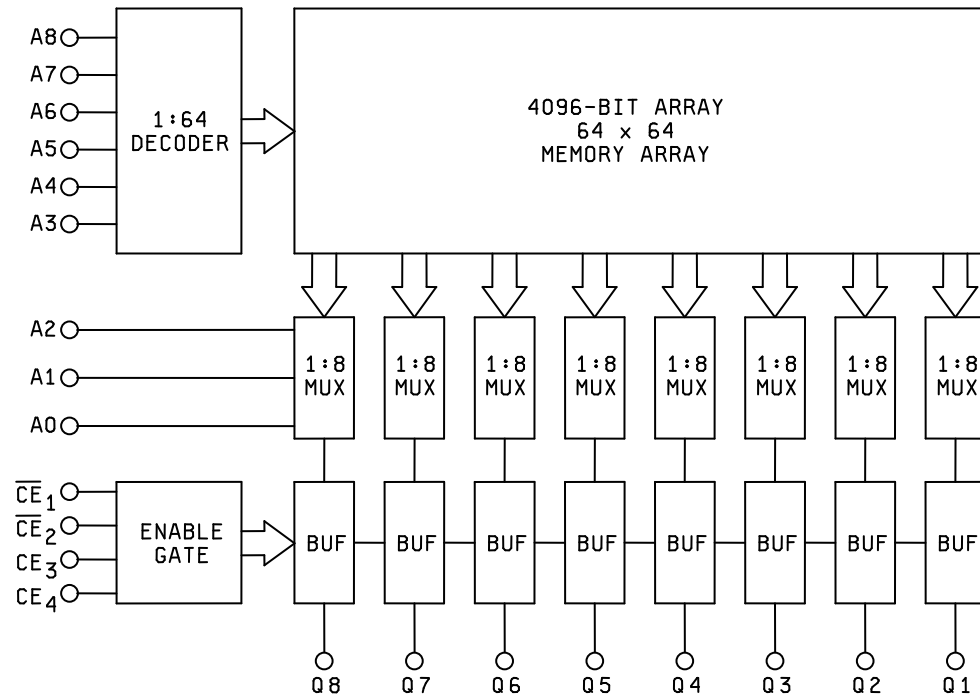


FIGURE 5. Logic diagrams – Continued.

LOGIC CIRCUIT G
(Device type 02)

FIGURE 5. Logic diagrams – Continued.

LOGIC CIRCUIT G
(Device types 04 and 05)

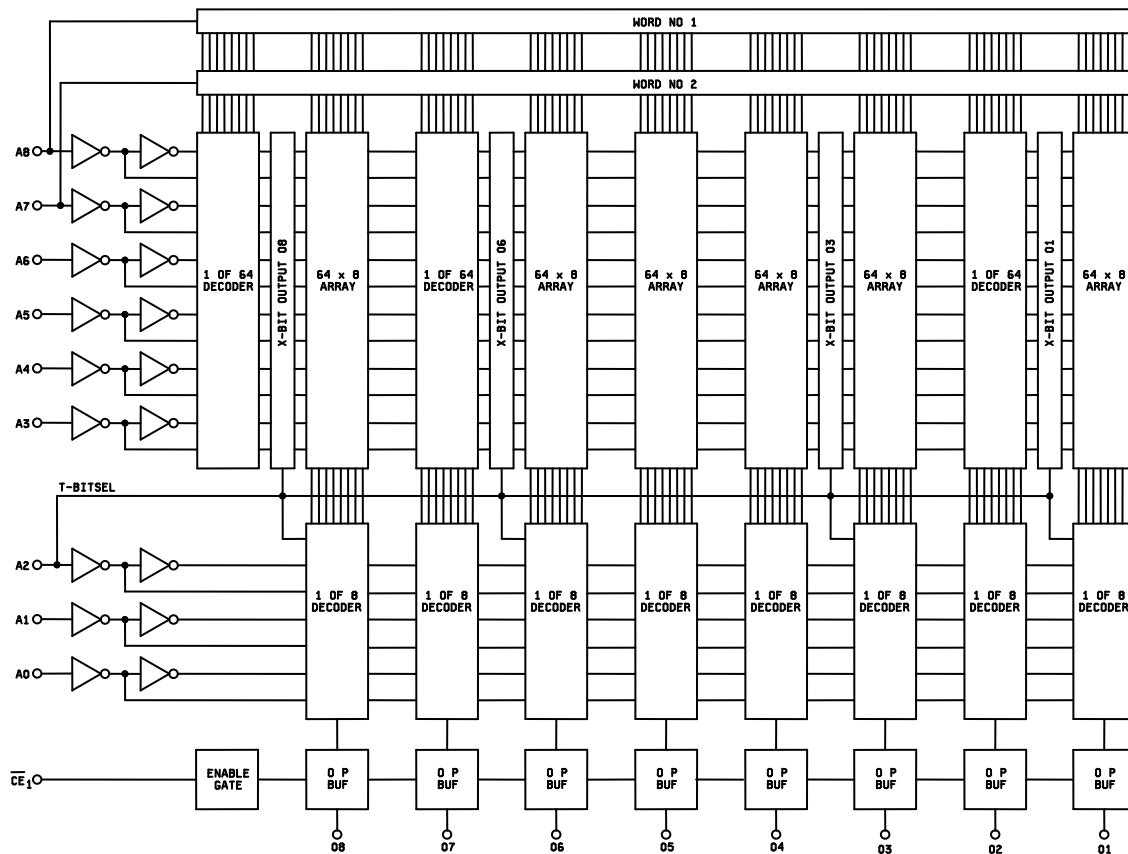
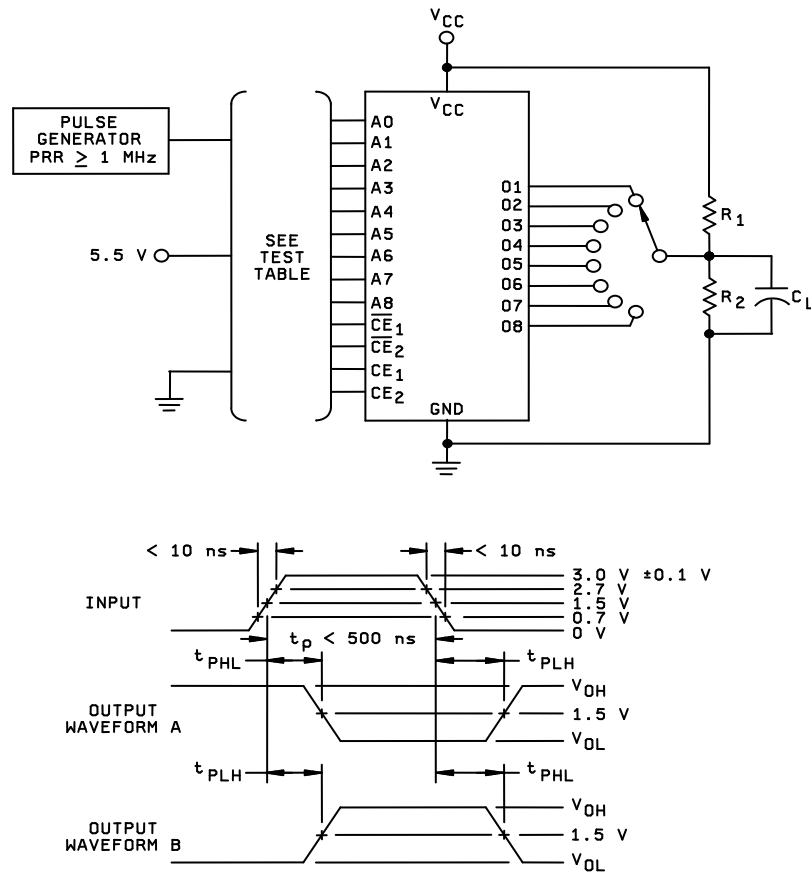


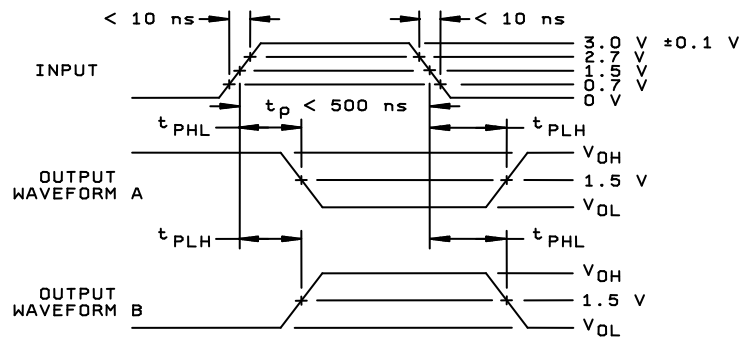
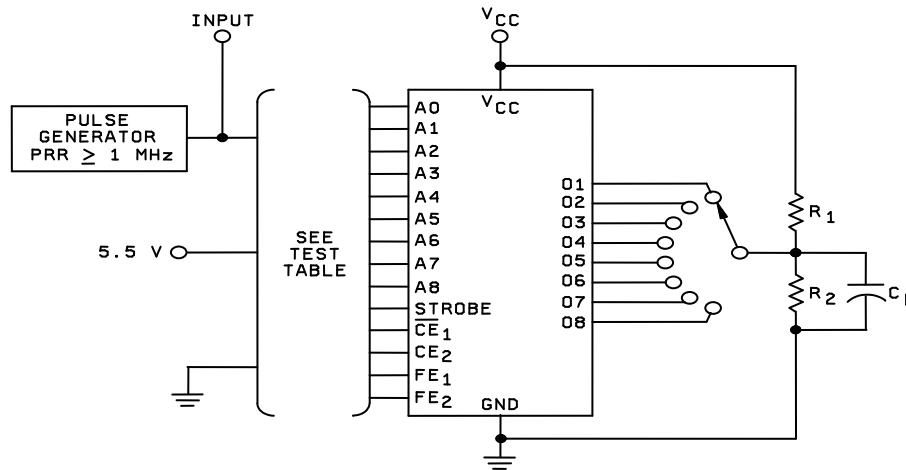
FIGURE 5. Logic diagrams – Continued.

Device types 01 and 02

NOTES:

1. Test table for devices programmed in accordance with an altered item drawing may be replaced by the equivalent tests which apply to the specific program configuration for the resulting read-only memory
2. $C_L = 30 \text{ pF}$ minimum, including jig and probe capacitance, $R_1 = 330 \Omega \pm 25\%$, and $R_2 = 680 \Omega \pm 20\%$.
3. Outputs may be under load simultaneously.

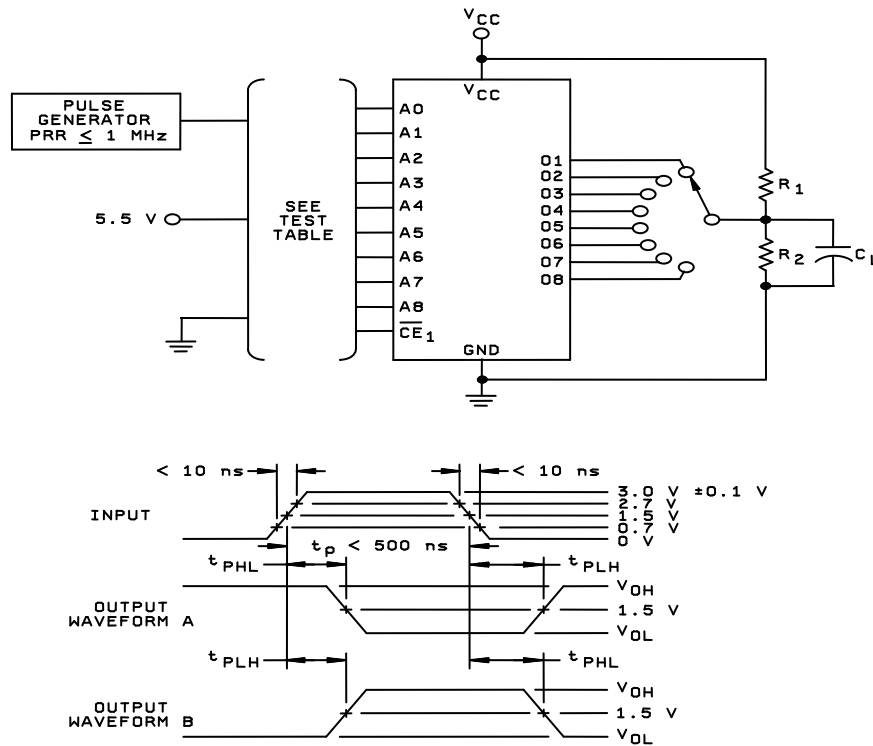
FIGURE 6. Switching time test circuit.

Device type 03

NOTES:

1. Test table for devices programmed in accordance with an altered item drawing may be replaced by the equivalent tests which apply to the specific program configuration for the resulting read-only memory
2. $C_L = 30$ pF minimum, including jig and probe capacitance, $R_1 = 330 \Omega \pm 25\%$, and $R_2 = 680 \Omega \pm 20\%$.
3. Outputs may be under load simultaneously.

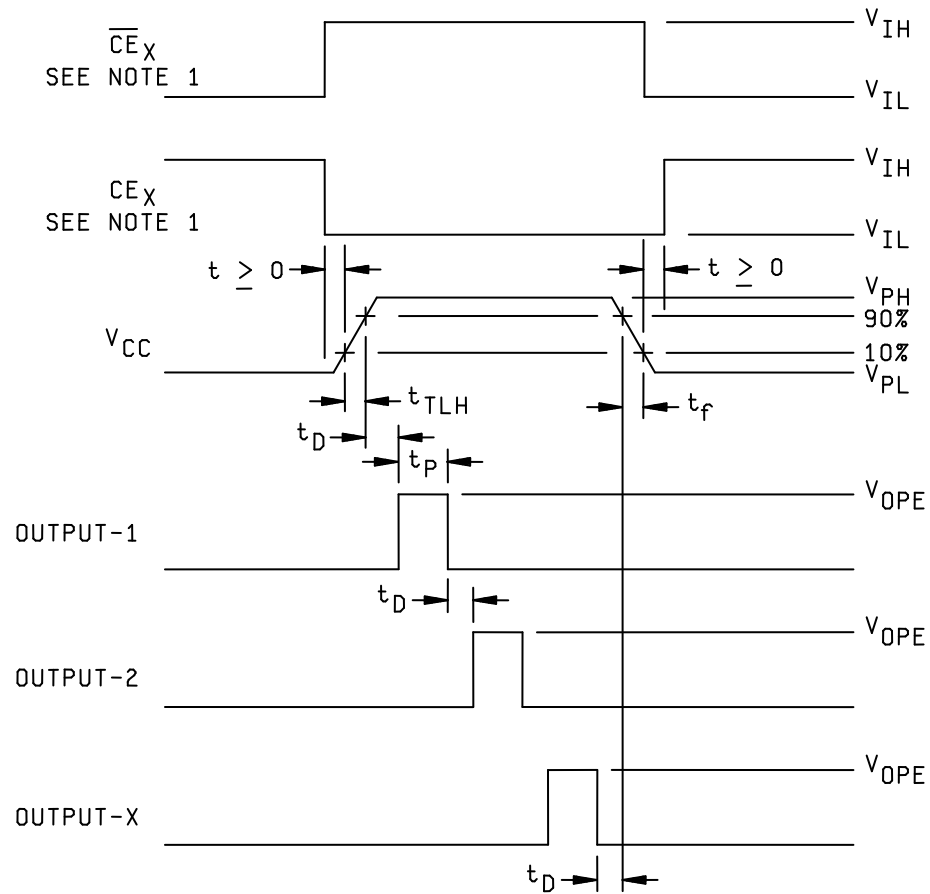
FIGURE 6. Switching time test circuit – Continued.

Device types 04 and 05

NOTES:

1. Test table for devices programmed in accordance with an altered item drawing may be replaced by the equivalent tests which apply to the specific program configuration for the resulting read-only memory
2. $C_L = 30$ pF minimum, including jig and probe capacitance, $R_1 = 330 \Omega \pm 25\%$, and $R_2 = 680 \Omega \pm 20\%$.
3. Outputs may be under load simultaneously.

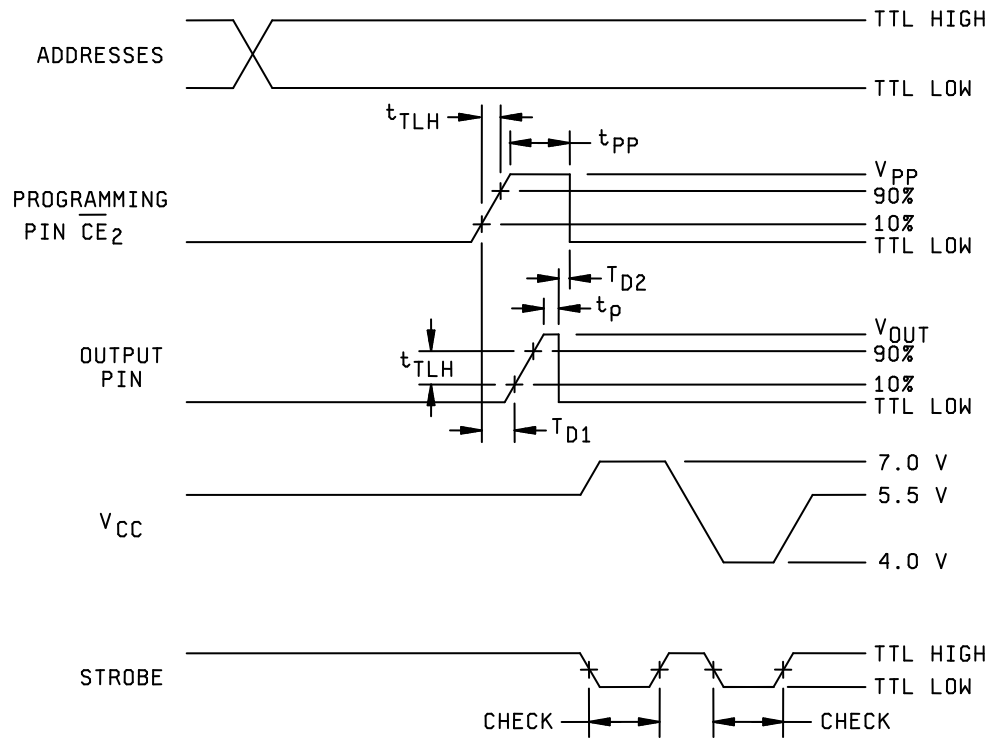
FIGURE 6. Switching time test circuit – Continued.



NOTES:

1. Disregard for devices with no chip enable inputs.
2. All other waveforms characteristics shall be as specified in table IVA.

FIGURE 7a. Programming voltage waveforms during programming for circuit A.

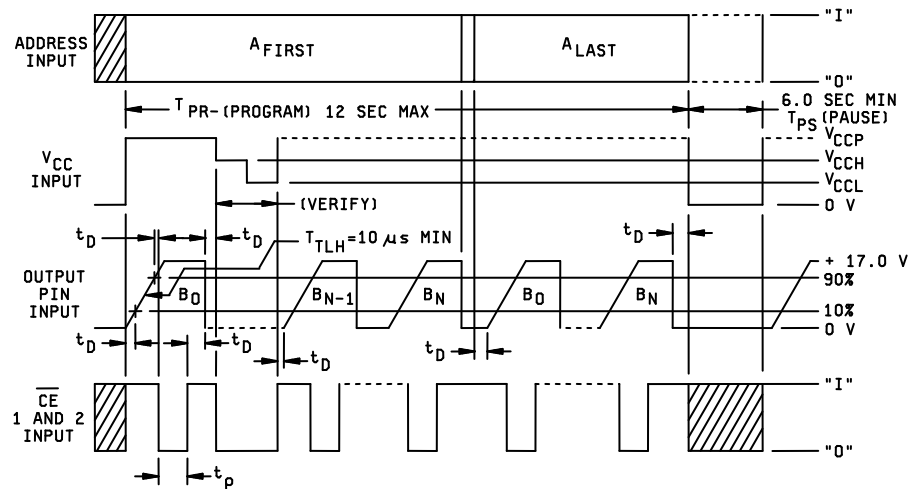


NOTES:

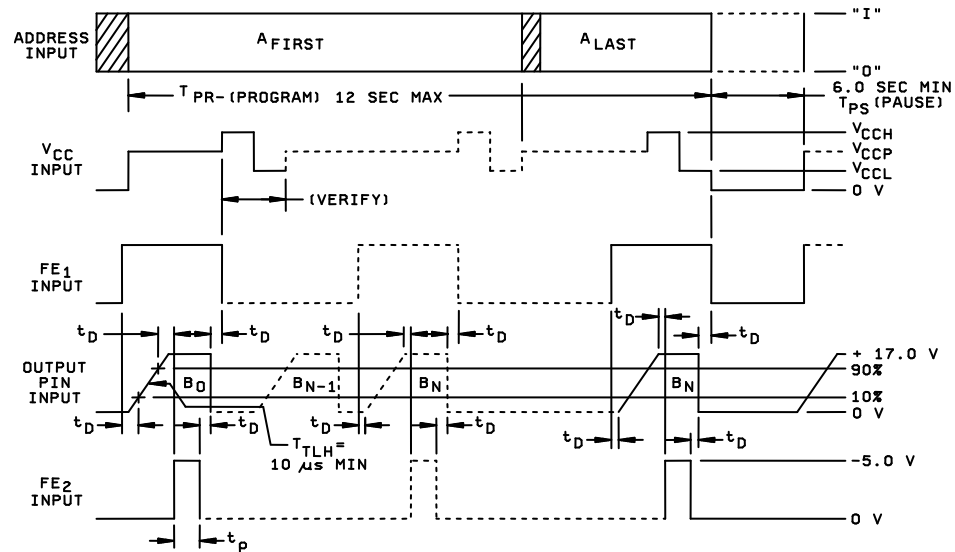
1. Output load is 0.2 mA and 12 mA during 7.0 V and 4.0 V check, respectively.
2. All other waveform characteristics shall be as specified in table IVB.
3. $\overline{CE}_1$ is the programming pin for device types 04 and 05.

FIGURE 7b. Programming voltage waveforms during programming for circuit B.

Device types 01 and 02

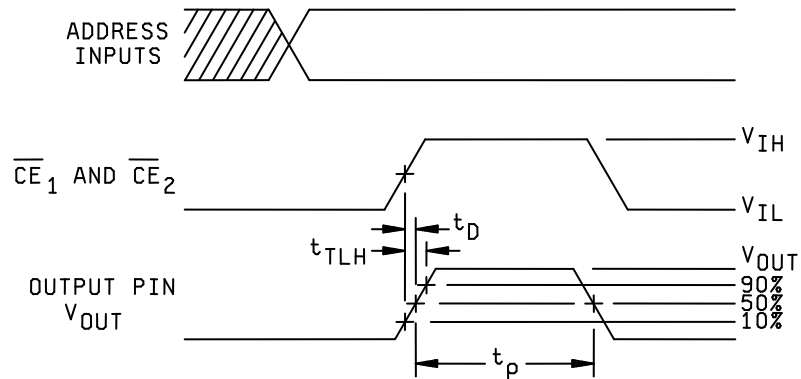


Device type 03



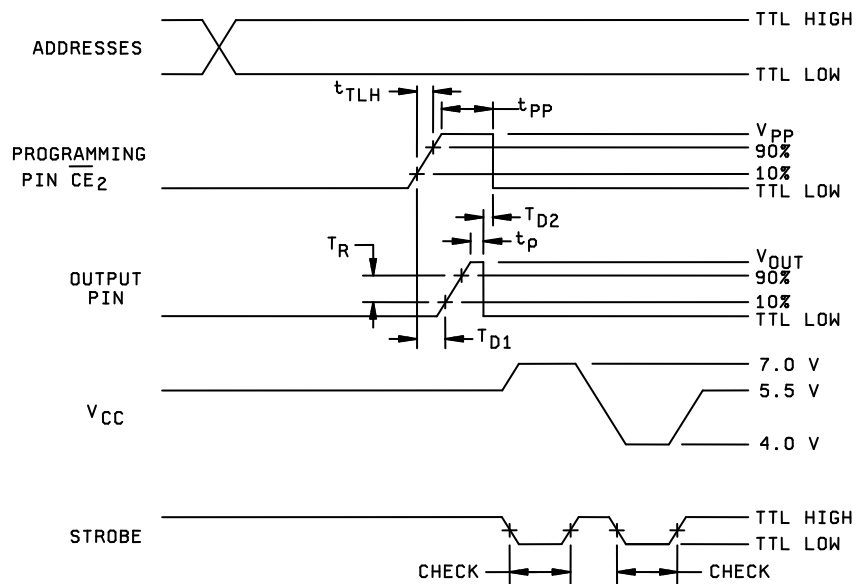
NOTE: All other waveform characteristics shall be as specified in table IVC.

FIGURE 7c. Programming voltage waveforms during programming for circuits C and H.



NOTE: All other waveform characteristics shall be as specified in table IVD.

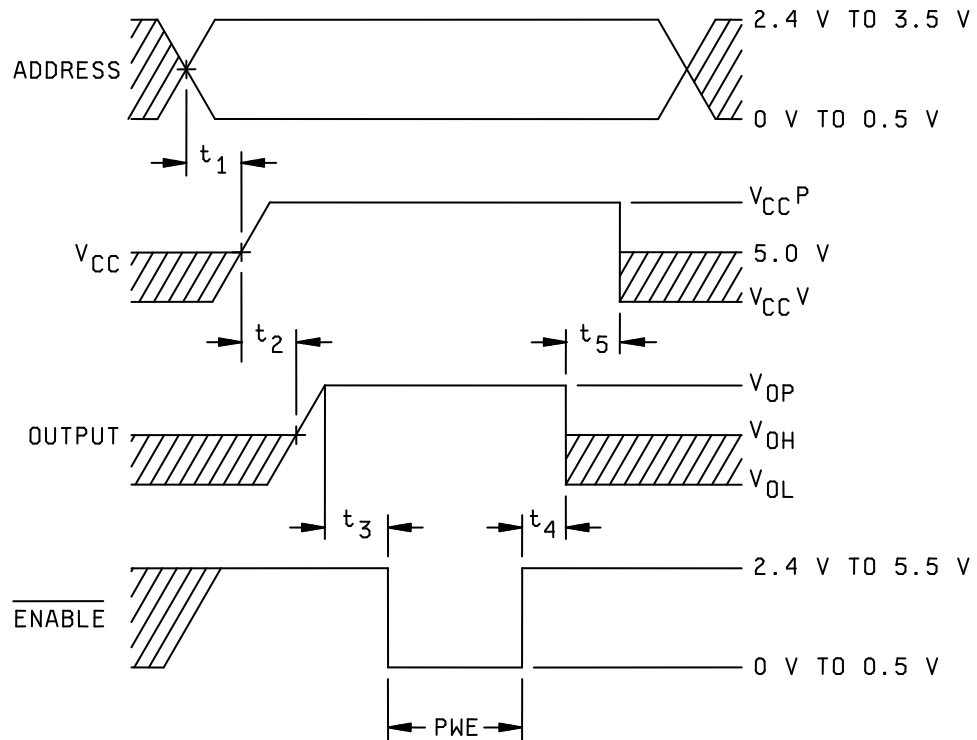
FIGURE 7d Programming voltage waveforms during programming for circuit D.



NOTES:

1. Output load is 0.2 mA and 12 mA during 7.0 V and 4.0 V check, respectively.
2. All other waveform characteristics shall be as specified in table IVF.

FIGURE 7f. Programming voltage waveforms during programming for circuit F.

FIGURE 7g. Programming voltage waveforms during programming for circuit G.

4. VERIFICATION

4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. Screening shall be in accordance with MIL-PRF-38535 and shall be conducted on all devices prior to qualification and quality conformance inspection. The following additional criteria shall apply:

- a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
- c. Additional screening for space level product shall be as specified in MIL-PRF-38535, appendix B.
- d. Class B devices processed to an altered item drawing may be programmed either before or after burn-in at the manufacturer's discretion. The required electrical testing shall include, as a minimum, the final electrical tests for programmed devices as specified in table II herein. Class S devices processed by the manufacturer to an altered item drawing shall be programmed prior to burn-in.

TABLE II. Electrical test requirements.

MIL-PRF-38535 test requirements	Subgroups (see table III) <u>1/</u> , <u>2/</u> , <u>3/</u>	
	Class S devices	Class B devices
Interim electrical parameters	1	1
Final electrical test parameters for unprogrammed devices	1*, 2, 3, 7*, 8	1*, 2, 3, 7*, 8
Final electrical test parameters for programmed devices	1*, 2, 3, 7*, 8, 9, 10, 11	1*, 2, 3, 7*, 8, 9
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8 9, 10, 11
Group B end-point electrical parameters when using the method 5005 QCI option	1, 2, 3, 7, 8, 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8
Group D test requirements	1, 2, 3, 7, 8	1, 2, 3, 7, 8

1/ * indicates PDA applies to subgroups 1 and 7.

2/ Any or all subgroups may be combined when using high-speed testers.

3/ Subgroups 7 and 8 shall consist of verifying the pattern specified.

4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.

4.4 Technology Conformance inspection (TCI). Technology conformance inspection shall be in accordance with MIL-PRF-38535 and as specified herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection. Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:

- a. Electrical test requirements shall be as specified in table II herein.
- b. Subgroups 4, 5, and 6 shall be omitted.
- c. For unprogrammed devices, a sample shall be selected to satisfy programmability requirements prior to performing subgroups 9, 10, and 11. Twelve devices shall be submitted to programming (see 3.3.2.1). If more than 2 devices fail to program, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 24 total devices with no more than 4 total device failures allowed.
- d. For unprogrammed devices, 10 devices from the programmability sample shall be submitted to the requirements of group A, subgroups 9, 10, and 11. If more than two total devices fail in all three subgroups, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 20 total devices with no more than 4 total device failures allowed.

TABLE III. Group A inspection for device type 01.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X,Z Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit		
				A7	A6	A5	A4	A3	A2	A1	A0	O1	O2	O3	GND	O4	O5	O6	O7	O8	CE ₄	CE ₃	$\overline{\text{CE}}_2$	$\overline{\text{CE}}_1$	NC	A8	V _{cc}		Min	Max			
1 T _C =25°C	V _{IC}		1	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA			GND												4.5V	A7		-1.5	V		
			2													"											"	A6		"	"		
			3													"											"	A5		"	"		
			4													"											"	A4		"	"		
			5													"											"	A3		"	"		
			6													"											"	A2		"	"		
			7													"											"	A1		"	"		
			8													"											"	A0		"	"		
			9													"											"	CE ₄		"	"		
			10													"						-10mA	-10mA				"	CE ₃		"	"		
			11													"							-10mA	-10mA				"	CE ₂		"	"	
			12													"								-10mA	-10mA			"	CE ₁		"	"	
			13													"												"	A8		"	"	
	V _{OL}	3007	14	1/2/	1/3/	1/	1/	1/	1/	1/	1/	1/2/	8 mA	8 mA	8 mA	"						2.4V	2.4V	0.5V	0.5V		-10mA	"	O1		0.5	V	
		"	15	"	"	"	"	"	"	"	"	"	"	"	"	"						"	"	"	"	"	"	"	"	O2		"	"
		"	16	"	"	"	"	"	"	"	"	"	"	"	"	"	8 mA					"	"	"	"	"	"	"	"	O3		"	"
		"	17	"	"	"	"	"	"	"	"	"	"	"	"	"		8 mA				"	"	"	"	"	"	"	"	O4		"	"
		"	18	"	"	"	"	"	"	"	"	"	"	"	"	"			8 mA			"	"	"	"	"	"	"	"	O5		"	"
		"	19	"	"	"	"	"	"	"	"	"	"	"	"	"			8 mA			8 mA		"	"	"	"	"	"	O6		"	"
		"	20	"	"	"	"	"	"	"	"	"	"	"	"	"				8 mA		8 mA		"	"	"	"	"	"	O7		"	"
		"	21	13/14/	13/14/	13/14/	13/14/	13/14/	13/14/	13/14/	13/14/	13/14/	13/14/	"	"	"							"	"	"	"	"	13/14/	"	O8		"	"
		I _{IL1}	3009	22	0.5V	0.5V	0.5V	0.5V	0.5V	0.5V	0.5V	0.5V	0.5V			"												5.5V	A7	-1.0	-250	μA	
			"	23												"												"	A6		"	"	
	"		24												"												"	A5		"	"		
	"		25												"												"	A4		"	"		
	"		26												"												"	A3		"	"		
	"		27												"												"	A2		"	"		
	"		28												"												"	A1		"	"		
	"		29												"												"	A0		"	"		
	"		30												"								0.5V	0.5V			"	CE ₄		"	"		
	"		31												"									0.5V	0.5V			"	CE ₃		"	"	
	"	32												"										0.5V	0.5V		"	CE ₂		"	"		
I _{IL2}	"	33												"							0.5V	0.5V				"	CE ₁	"	-1000	μA			
	"	34												"												"	A8		-1000	"			
I _{HL1}	3010	35	5.5V	5.5V	5.5V	5.5V	5.5V	5.5V	5.5V	5.5V	5.5V			"													"	A7		50	μA		
	"	36												"													"	A6		"	"		
	"	37												"												"	A5		"	"			
	"	38												"												"	A4		"	"			
	"	39												"												"	A3		"	"			
	"	40												"												"	A2		"	"			
	"	41												"												"	A1		"	"			
	"	42												"												"	A0		"	"			
	"	43												"								5.5V	5.5V			"	CE ₄		"	"			
	"	44												"									5.5V	5.5V			"	CE ₃		"	"		
"	45												"										5.5V	5.5V		"	CE ₂		"	"			
I _{HL2}	"	46												"											5.5V	"	A8		"	"			
	"	47												"								4.5V				"	$\overline{\text{CE}}_2$		100				

See footnotes at end of table.

TABLE III. Group A inspection for device type 01 – Continued.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X,Z Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit
				A7	A6	A5	A4	A3	A2	A1	A0	O1	O2	O3	GND	O4	O5	O6	O7	O8	CE ₄	CE ₃	CE ₂	CE ₁	NC	A8	V _{CC}		Min	Max	
1 T _C =+25°C	I _{CEX}		48 49 50 51 52 53 54 55	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	15/ 1/ " " " " " "	5.2V	5.2V	5.2V	GND " " " 5.2V	5.2V	5.2V	5.2V	5.2V	5.2V	5.2V					15/ 1/ " " " " " "	5.5V " " " " " " "	O1 O2 O3 O4 O5 O6 O7 O8		100	μA
	I _{CC}	3005	56	GND	GND	GND	GND	GND	GND	GND	GND				"						5.2V	5/	5/	GND	GND		GND	"	V _{CC}		185
2	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = 125°C and V _{CC} tests are omitted.																														
3	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = -55°C and V _{CC} tests are omitted.																														
7 T _C =25°C	Functional test	3014	57	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	GND	6/	6/	6/	6/	6/	6/	6/	6/	6/		6/	6/	Outputs		6/	
8	Same tests, terminal conditions, and limits as for subgroup 7, except T _C = 125°C.																														
9 T _C =25°C	t _{PLH1}	GALPAT Fig. 6	58	7/	7/	7/	7/	7/	7/	7/	7/	9/	9/	9/	GND	9/	9/	9/	9/	9/	5.5V	5.5V	GND	GND		7/	7/	Outputs		90	ns
	t _{PHL1}	GALPAT Fig. 6	59	7/	7/	7/	7/	7/	7/	7/	7/	"	"	"	"	"	"	"	"	"	5.5V	5.5V	GND	GND		7/	7/	"		90	"
	t _{PLH2}	Sequential Fig. 6	60	8/	8/	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/		8/	8/	"		50	"
	t _{PHL2}	Sequential Fig. 6	61	8/	8/	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/		8/	8/	"		50	"
10	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = 125°C.																														
11	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = -55°C.																														

See footnotes at end of table.

TABLE III. Group A inspection for device type 02.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X,Z Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit			
				A7	A6	A5	A4	A3	A2	A1	A0	O1	O2	O3	GND	O4	O5	O6	O7	O8	CE ₄	CE ₃	$\overline{\text{CE}}_2$	$\overline{\text{CE}}_1$	NC	A8	V _{CC}		Min	Max				
1 T _C =25°C	V _{IC}		1 2 3 4 5 6 7 8 9 10 11 12 13	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA	GND													4.5V	A7 A6 A5 A4 A3 A2 A1 A0 CE ₄ CE ₃ CE ₂ CE ₁ A8		-1.5	V			
		V _{OIL}	3007	14 15 16 17 18 19 20 21	1/ 2/ " " " " " " 16/ " " 13/ " "	1/ 3/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ 2/ " " " " " " 16/ " " 13/ " "	8 mA	8 mA	8 mA			8 mA	8 mA	8 mA	8 mA	2.4V	2.4V	0.5V	0.5V		-10mA	O1 O2 O3 O4 O5 O6 O7 O8		0.5	V				
			V _{OH}	3006	22 23 24 25 26 27 28 29	" " " " " " " " " " " " 17/ " "	1/ 10/ " " " " " " " " " " 17/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ 25/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	1/ " " " " " " 16/ " " 13/ " "	-2mA	-2mA	-2mA		-2mA	-2mA	-2mA	-2mA							1/ 10/ " " " " " " " " " " 17/ " "	O1 O2 O3 O4 O5 O6 O7 O8	2.4		V			
				I _{IL1}	3009	30 31 32 33 34 35 36 37 38 39 40	0.5V "	0.5V "	0.5V "	0.5V "	0.5V "	0.5V "	0.5V "																0.5V " " " " " " " " " " 0.5V " " " " " " " " " "	A7 A6 A5 A4 A3 A2 A1 A0 CE ₄ CE ₃ CE ₂ CE ₁ A8	-1.0	-250	μA	
					I _{IL2} 24/	" "	41 42																	0.5V	0.5V				0.5V " "	CE ₂ CE ₃	" "	-1000 -1000	μA	
						I _{IH1}	3010	43 44 45 46 47 48 49 50 51 52 53 54	5.5V "	5.5V "	5.5V "	5.5V "	5.5V "	5.5V "	5.5V "											5.5V	5.5V		5.5V		5.5V "	A7 A6 A5 A4 A3 A2 A1 A0 CE ₄ CE ₃ CE ₂ CE ₁ A8		50
					I _{IH2} 23/		" "	55																		4.5V				5.5V	$\overline{\text{CE}}_2$		100	μA

See footnotes at end of table.

TABLE III. Group A inspection for device type 02 – Continued.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X,Z	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit			
			Test no.	A7	A6	A5	A4	A3	A2	A1	A0	O1	O2	O3	GND	O4	O5	O6	O7	O8	CE ₄	CE ₃	CE ₂	CE ₁	NC	A8	V _{CC}		Min	Max				
1 T _C =25°C	I _{OHZ}		56									5.2V	5.2V	5.2V	GND						GND	GND	5.5V	5.5V			5.5V	O1		100	μA			
			57																									O2						
			58																									O3						
			59																									O4						
			60																									O5						
			61																									O6						
			62																									O7						
			63																									O8						
	I _{OLZ}		64										0.5V	0.5V	0.5V													O1		-100	μA			
			65																									O2						
			66																									O3						
		67																									O4							
		68																									O5							
I _{CC}	3005	71	GND	GND	GND	GND	GND	GND	GND	GND											5/	5/	GND	GND		GND	V _{CC}		185	mA				
	I _{OS}	3011	73	1/	1/ 10/	1/	1/	1/	1/	1/	1/	GND	GND								5.5V	5.5V			1/ 10/	O1	-10	-100	mA					
			74																									O2						
		75											GND														O3							
		76													GND												O4							
		77														GND											O5							
		78																GND									O6							
		79																	GND								O7							
	80	18/	18/	18/	18/	18/	18/	18/	18/	18/														18/	O8									
2	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = 125°C and V _{IC} tests are omitted.																																	
3	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = -55°C and V _{IC} tests are omitted.																																	
7 T _C =25°C	Functional test	3014	81	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	GND	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	Outputs		6/	ns
8	Same tests, terminal conditions, and limits as for subgroup 7, except T _C = 125°C and T _C = -55°C.																																	
9 T _C =25°C	t _{PLH1}	GALPAT Fig. 6 GALPAT Fig. 6 Sequential Fig. 6 Sequential Fig. 6	82	7/	7/	7/	7/	7/	7/	7/	7/	9/	9/	9/	GND	9/	9/	9/	9/	9/	5.5V	5.5V	GND	GND		7/	7/	Outputs		90	ns			
	t _{PHL1}		83	7/	7/	7/	7/	7/	7/	7/	7/	"	"	"	"	"	"	"	"	"	5.5V	5.5V	GND	GND		7/	7/	"		90	"			
	t _{PLH2}		84	8/	8/	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/		8/	8/	"		50	"			
	t _{PHL2}		85	8/	8/	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/		8/	8/	"		50	"			
10	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = 125°C.																																	
11	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = -55°C.																																	

See footnotes at end of table.

TABLE III. Group A inspection for device type 03.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; inputs not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit	
				A3	A4	A5	A6	A7	A8	O1	O2	O3	O4	FE2	GND	FE1	O5	O6	O7	O8	Strobe	$\overline{\text{CE}}_2$	$\overline{\text{CE}}_1$	A0	A1	A2	V _{CC}		Min	Max		
1 T _C =25°C	V _{IC}		1 2 3 4 5 6 7 8 9 10 11 12 13 14	-10mA	-10mA	-10mA	-10mA	-10mA	-10mA					-10mA		-10mA					-10mA	-10mA		-10mA	-10mA	-10mA	4.5V	A3 A4 A5 A6 A7 A8 FE2 FE1 Strobe CE ₂ CE ₁ A0 A1 A2		-1.5	V	
		V _{OL}	3007	15 16 17 18 19 20 21 22	1/	1/	1/	1/	1/	1/	8mA	8mA	8mA	8mA	GND		GND				2.4V	2.4V	0.5V	1/	1/	1/		O1 O2 O3 O4 O5 O6 O7 O8		0.5	V	
		V _{OH}	3006	23 24 25 26 27 28 29 30						1/ 10/	-2mA	-2mA	-2mA	-2mA				-2mA	-2mA	-2mA	-2mA								O1 O2 O3 O4 O5 O6 O7 O8	2.4		V
		I _{IL1}	3009	31 32 33 34 35 36 37 38 39 40 41 42 43 44	0.5V	0.5V	0.5V	0.5V	0.5V	0.5V					0.5V		0.5V				0.5V	0.5V		0.5V	0.5V	0.5V	5.5V	A3 A4 A5 A6 A7 A8 FE ₂ FE ₁ Strobe CE ₂ CE ₁ A0 A1 A2	-1.0	-100	μA	
		I _{HI1}	3010	45 46 47 48 49 50 51 52 53 54 55 56	5.5V	5.5V	5.5V	5.5V	5.5V	5.5V											5.5V	5.5V		5.5V	5.5V	5.5V	5.5V		A3 A4 A5 A6 A7 A8 Strobe CE ₂ CE ₁ A0 A1 A2		50	μA

See footnotes at end of table.

TABLE III. Group A inspection for device type 03 – Continued.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Cases J,K,X	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	Measured terminal	Test limits		Unit		
			Test no.	A3	A4	A5	A6	A7	A8	O1	O2	O3	O4	FE ₂	GND	FE ₁	O5	O6	O7	O8	Strobe	$\overline{\text{CE}}_2$	$\overline{\text{CE}}_1$	A0	A1	A2	V _{CC}		Min	Max			
1 T _C =25°C	I _{OHZ}		57							5.2V	5.2V	5.2V	5.2V		GND						0.5V	2.4V	0.5V				5.5V	O1		100	μA		
			58												"						"	"	"				"	O2		"	"		
			59												"			5.2V	5.2V		"	"	"				"	O3		"	"		
			60												"						"	"	"				"	O4		"	"		
		61												"					5.2V		"	"	"				"	O5		"	"		
		62												"					5.2V	5.2V	"	"	"				"	O6		"	"		
		63												"						5.2V		"	"				"	O7		"	"		
		64												"						5.2V		"	"				"	O8		"	"		
	I _{OLZ}		65							0.5V	0.5V	0.5V	0.5V			"					"	"	"				"	O1		-100	μA		
			66												"						"	"	"				"	O2		"	"		
			67												"						"	"	"				"	O3		"	"		
			68												"			0.5V	0.5V		"	"	"				"	O4		"	"		
	69												"					0.5V	0.5V	"	"	"				"	O5		"	"			
	70												"						0.5V		"	"	"			"	O6		"	"			
	71												"							"	"	"				"	O7		"	"			
	72												"						0.5V	0.5V	"	"	"			"	O8		"	"			
	I _{CC}	3005	73	GND	GND	GND	GND	GND	GND					GND	"	GND					GND	GND	GND				"	V _{CC}		185	mA		
	I _{OS}	3011	74	1/	1/	1/	1/ 25/	1/	1/ 10/	GND					"						"	5.5V	"	1/	1/ 10/	1/	"	O1	-10	-100	mA		
		75	"	"	"	"	"	"	"		GND				"						"	"	"	"	"	"	"	O2	"	"	"		
		76	"	"	"	"	"	"	"			GND			"						"	"	"	"	"	"	"	O3	"	"	"		
		77	"	"	"	"	"	"	"						"						"	"	"	"	"	"	"	O4	"	"	"		
		78	"	"	"	"	"	"	"						"		GND				"	"	"	"	"	"	"	O5	"	"	"		
		79	"	"	"	"	"	"	"						"			GND			"	"	"	"	"	"	"	O6	"	"	"		
		80	"	"	"	"	"	"	"						"				GND		"	"	"	"	"	"	"	O7	"	"	"		
		81	"	"	"	"	"	"						"					GND	"	"	"	"	"	"	"	O8	"	"	"			
2	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = 125°C and V _{CC} tests are omitted.																																
3	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = -55°C and V _{CC} tests are omitted.																																
7 T _C =25°C	Functional test	3014	82	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	GND	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	Outputs		6/			
8	Same tests, terminal conditions, and limits as for subgroup 7, except T _C = 125°C and T _C = -55°C.																																
9 T _C =25°C	t _{PLH1}	GALPAT Fig. 6	83	7/	7/	7/	7/	7/	7/	9/	9/	9/	9/	GND	GND	GND	9/	9/	9/	9/	GND	5.5V	GND	7/	7/	7/	7/	Outputs		90	ns		
	t _{PHL1}	GALPAT Fig. 6	84	7/	7/	7/	7/	7/	7/	"	"	"	"	"	"	"	"	"	"	"	"	"	"	7/	7/	7/	7/	"		90	"		
	t _{PLH2}	Sequen-tial Fig. 6	85	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/	"		50	"		
	t _{PHL2}	Sequen-tial Fig. 6	86	8/	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/	"		50	"		
10	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = 125°C.																																
11	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = -55°C.																																

See footnotes at end of table.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Case Y Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	Measured terminal	Test limits		Unit	
				A0	A1	A2	A3	A4	O1	O2	O3	O4	GND	O5	O6	O7	O8	CE ₁	A5	A6	A7	A8	V _{CC}		Min	Max		
1 T _C =25°C	V _{IC}		1 2 3 4 5 6 7 8 9 10	-10mA	-10mA	-10mA	-10mA	-10mA					GND										4.5V	A0 A1 A2 A3 <u>A4</u> CE ₁ A5 A6 A7 A8		-1.5	V	
	V _{OL}	3007	11 12 13 14 15 16 17 18	2.4V	1/ 3/ "	1/ "	1/ "	1/ "	8mA	8mA	8mA		"					0.5V	1/ "	1/ "	1/ "	1/ "	"	O1 O2 O3 O4 O5 O6 O7 O8		0.5	V	
	I _{IL}	3009	19 20 21 22 23 24 25 26 27 28	0.5V	0.5V	0.5V	0.5V	0.5V					"					0.5V					5.5V	A0 A1 A2 A3 <u>A4</u> CE ₁ A5 A6 A7 A8	-1.0	-250	μA	
	I _{IH1}	3010	29 30 31 32 33 34 35 36 37	5.5V	5.5V	5.5V	5.5V	5.5V					"						5.5V	5.5V	5.5V		5.5V	A0 A1 A2 A3 A4 A5 A6 A7 A8		50	μA	
	I _{IH2}	"	38										"					4.5V					"	CE ₁		100	μA	
	I _{CEX}		39 40 41 42 43 44 45 46						5.2V	5.2V	5.2V	5.2V	"		5.2V	5.2V	5.2V	5.2V					"	O1 O2 O3 O4 O5 O6 O7 O8			μA	
	I _{CC}	3005	47	GND	GND	GND	GND	GND					"				5.2V		GND	GND	GND	GND	GND	"	V _{CC}		155	mA

See footnotes at end of table.

TABLE III. Group A inspection for device type 04 – Continued.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Case Y Test no.	1 A0	2 A1	3 A2	4 A3	5 A4	6 O1	7 O2	8 O3	9 O4	10 GND	11 O5	12 O6	13 O7	14 O8	15 $\overline{CE}_1$	16 A5	17 A6	18 A7	19 A8	20 V_{CC}	Measured terminal	Test limits		Unit
2	Same tests, terminal conditions, and limits as for subgroup 1, except $T_C = 125^{\circ}\text{C}$ and V_{IC} tests are omitted.																										
3	Same tests, terminal conditions, and limits as for subgroup 1, except $T_C = -55^{\circ}\text{C}$ and V_{IC} tests are omitted.																										
7 $T_C=25^{\circ}\text{C}$	Functional test	3014	48	6/	6/	6/	6/	6/	6/	6/	6/	6/	GND	6/	6/	6/	6/	6/	6/	6/	6/	6/	6/	Outputs		6/	
8	Same tests, terminal conditions, and limits as for subgroup 7, except $T_C = 125^{\circ}\text{C}$ and $T_C = -55^{\circ}\text{C}$.																										
9 $T_C=25^{\circ}\text{C}$	t_{PLH1}	GALPAT Fig. 6	49	Z/	Z/	Z/	Z/	Z/	9/	9/	9/	9/	GND	9/	9/	9/	9/	GND	Z/	Z/	Z/	Z/	Z/	Outputs		80	ns
	t_{PHL1}	GALPAT Fig. 6	50	Z/	Z/	Z/	Z/	Z/	"	"	"	"	"	"	"	"	"	GND	Z/	Z/	Z/	Z/	Z/	"		80	"
	t_{PLH2}	Sequential Fig. 6	51	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/	8/	8/	"		50	"
	t_{PHL2}	Sequential Fig. 6	52	8/	8/	8/	8/	8/	"	"	"	"	"	"	"	"	"	8/	8/	8/	8/	8/	8/	"		50	"
10	Same tests, terminal conditions, and limits as for subgroup 9, except $T_C = 125^{\circ}\text{C}$.																										
11	Same tests, terminal conditions, and limits as for subgroup 9, except $T_C = -55^{\circ}\text{C}$.																										

See footnotes at end of table.

TABLE III. Group A inspection for device type 05.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Case Y Test no.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	Measured terminal	Test limits		Unit
				A0	A1	A2	A3	A4	O1	O2	O3	O4	GND	O5	O6	O7	O8	$\overline{\text{CE}}_1$	A5	A6	A7	A8	V _{CC}		Min	Max	
1 T _C =25°C	V _{IC}		1	-10mA	-10mA	-10mA	-10mA	-10mA					GND										4.5V	A0		-1.5	V
			2																					A1			
			3																					A2			
			4																					A3			
			5																					A4			
			6															-10mA	-10mA					CE ₁			
			7																	-10mA				A5			
			8																		-10mA			A6			
			9																			-10mA		A7			
			10																			-10mA		A8			
	V _{OL}	3007	11	2.4V	1/ 3/	1/ 11/	1/ 11/	1/ 11/	12/	12/	12/	12/						0.5V	1/	1/	1/	1/		O1		0.5	V
			12																					O2			
			13																					O3			
			14																					O4			
			15																					O5			
			16																					O6			
			17																					O7			
			18	20/	20/	20/	20/	20/									12/		20/	20/	20/	20/		O8			
	V _{OH}	3006	19	1/	1/	1/	1/	1/	-2mA	-2mA	-2mA	-2mA							1/	1/	1/	1/		O1	2.4		V
			20																					O2			
			21																					O3			
			22																					O4			
			23																					O5			
			24																					O6			
			25																					O7			
			26	21/	21/	21/	21/	21/									-2mA		21/	21/	21/	21/		O8			
	I _{IL}	3009	27	0.5V	0.5V	0.5V	0.5V	0.5V															5.5V	A0	-1.0	-250	μA
			28																					A1			
			29																					A2			
			30																					A3			
			31																					A4			
			32															0.5V	0.5V	0.5V	0.5V	0.5V		CE ₁			
			33																					A5			
			34																					A6			
			35																					A7			
			36																					A8			
	I _{IH1}	3010	37	5.5V	5.5V	5.5V	5.5V	5.5V																A0		50	μA
			38																					A1			
			39																					A2			
			40																					A3			
			41																					A4			
			42																					A5			
			43																					A6			
			44																					A7			
			45																					A8			
	I _{IH2}		46															4.5V						$\overline{\text{CE}}_1$		100	

See footnotes at end of table.

TABLE III. Group A inspection for device type 05 – Continued.

Terminal conditions: Outputs not designated are open or resistive coupled to GND or voltage; input not designated are high ≥ 2.0 V, low ≤ 0.8 V, or open.

Subgroup	Symbol	MIL-STD-883 method	Case Y Test no.	1 A0	2 A1	3 A2	4 A3	5 A4	6 O1	7 O2	8 O3	9 O4	10 GND	11 O5	12 O6	13 O7	14 O8	15 CE ₁	16 A5	17 A6	18 A7	19 A8	20 V _{CC}	Measured terminal	Test limits Min Max		Unit	
1 T _C =25°C	I _{OHZ}		47						5.2V	5.2V	5.2V	5.2V	GND					5.5V					5.5V	O1		100	μA	
			48																					O2				
			49																					O3				
			50																					O4				
			51																					O5				
			52																					O6				
			53																					O7				
			54																					O8				
	I _{OLZ}		55							0.5V	0.5V	0.5V	0.5V												O1		-100	μA
			56																					O2				
			57																					O3				
			58																					O4				
			59																					O5				
			60																					O6				
			61																					O7				
			62																					O8				
	I _{CC}	3005	63	GND	GND	GND	GND	GND										GND	GND	GND	GND	GND		V _{CC}	-10	-100	mA	
	I _{OS}	3011	64	1/	1/	1/	1/	1/	GND										0.5V	1/	1/	1/	1/		O1			mA
			65																					O2				
			66																					O3				
			67																					O4				
			68																					O5				
			69																					O6				
			70																					O7				
			71	22/	22/	22/	22/	22/												22/	22/	22/	22/		O8			
2	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = 125°C and V _{CC} tests are omitted.																											
3	Same tests, terminal conditions, and limits as for subgroup 1, except T _C = -55°C and V _{CC} tests are omitted.																											
7 T _C =25°C	Functional test	3014	72	6/	6/	6/	6/	6/	6/	6/	6/	GND	6/	6/	6/	6/	GND	6/	6/	6/	6/	6/	Outputs		6/			
8	Same tests, terminal conditions, and limits as for subgroup 7, except T _C = 125°C and T _C = -55°C.																											
9 T _C =25°C	t _{PLH1}	GALPAT Fig. 6 GALPAT Fig. 6 Sequential Fig. 6 Sequential Fig. 6	73	7/	7/	7/	7/	7/	9/	9/	9/	9/	GND	9/	9/	9/	9/	GND	7/	7/	7/	7/	7/	Outputs		80	ns	
	t _{PHL1}		74	7/	7/	7/	7/	7/										GND	7/	7/	7/	7/	7/			80		
	t _{PLH2}		75	8/	8/	8/	8/	8/										8/	8/	8/	8/	8/	8/			40		
	t _{PHL2}		76	8/	8/	8/	8/	8/										8/	8/	8/	8/	8/	8/			40		
10	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = 125°C.																											
11	Same tests, terminal conditions, and limits as for subgroup 9, except T _C = -55°C.																											

See footnotes at end of table.

- 1/ For unprogrammed devices, select an appropriate address to acquire the desired output state.
- 2/ For unprogrammed devices (circuit D), apply 12.0 V on pin 8 (A0) and pin 1 (A7).
- 3/ For unprogrammed device types 01 and 02 (circuit B), apply 12.0 V on pin 2 (A6); for unprogrammed device types 04 and 05 (circuit B), apply 12.0 V on pin 2 (A1).
- 4/ For unprogrammed devices (circuit A), apply 11.0 V on pin 23 (A8).
- 5/ CE₄ and CE₃ may be "GND" or "2.4 V".
- 6/ The functional test shall verify that no fuses are blown for unprogrammed devices or that the altered item drawing pattern exists for programmed devices (see table II and 3.3.2.2). All bits shall be tested. The functional tests shall be performed with V_{CC} = 4.5 V and V_{CC} = 5.5 V. Terminal conditions shall be as follows:
 - a. Inputs: H = 3.0 V, L = 0.0 V.
 - b. Outputs: Output voltage shall be either:
 - (1) H = 2.4 V minimum and L = 0.5 V maximum when using a high-speed checker double comparator, or
 - (2) $H \geq 1.0$ V and $L < 1.0$ V when using a high-speed checker single comparator.
- 7/ GALPAT (PROGRAMMED PROM). This program will test all bits in the array, the addressing and interaction between bits for ac performance, t_{PLH1} and t_{PHL1}. Each bit in the pattern is fixed by being programmed with an "H" or "L". The GALPAT tests shall be performed with V_{CC} = 4.5 V and 5.5 V.

Description:

- Step 1. Word 0 is read.
- Step 2. Word 1 is read.
- Step 3. Word 0 is read.
- Step 4. Word 2 is read.
- Step 5. Word 0 is read.
- Step 6. The reading procedure continues back and forth between word 0 and the next higher numbered word until word 511 is reached, then increments to the next word and reads back and forth as in step 1 through step 6 and shall include all words.
- Step 7. Pass execution time = $(n^2 + n) \times \text{cycle time}$. $n = 512$.

- 8/ SEQUENTIAL (PROGRAMMED PROM). This program will test all bits in the array for t_{PLH2} and t_{PHL2}. The SEQUENTIAL tests shall be performed with V_{CC} = 4.5 V and 5.5 V.

Description:

- Step 1. Each word in the pattern is tested from the enable lines to the output lines for recovery.
- Step 2. Word 0 is addressed. Enable line is pulled high to low and low to high. t_{PHL2} and t_{PLH2} are
- Step 3. Word 1 is addressed. Same enable sequence as above.
- Step 4. The reading procedure continues until word 511 is reached.
- Step 5. Pass execution time = 512 x cycle time.

- 9/ The outputs are loaded per figure 6.
- 10/ For uprogrammed device types 01 and 02 (circuit C), apply 10.0 V on pin 23 (A8); 0.5 V on pin 2 (A6); and 5.0 V on all other address pins. For unprogrammed device type 03 (circuit C), apply 10.0 V on pin 6 (A8); 0.5 V on pin 22 (A1); and 5.0 V on all other address pins.
- 11/ For unprogrammed devices (circuit F), apply 12.0 V on pin 3 (A2) and 0.0 V on pin 4 (A3).
- 12/ I_{OL} = 8 mA for circuit B devices; I_{OL} = 16 mA for circuit F devices.

- 13/ For unprogrammed device types 01, 02, 04, and 05 (circuit G) select an appropriate address to obtain the desired output state.
- 14/ For programmed device type 02 (circuit G) apply 4.5 V to pin 24; 10.5 V to pin 1; 3.0 V to pins 23, 19, 18, 8, 7, 6, 4, 3, and 2; and 0.0 V to pins 21, 20, 12, and 5.
- 15/ For unprogrammed device type 01 (circuit G) apply 10.5 V to pins 6 and 1; 5.5 V to pin 24; 3.0 V to pins 23, 19, 18, 8, 7, 6, 4, 3, and 2; 0.0 V to pins 21, 20, 12, and 5.
- 16/ For programmed device type 02 (circuit G) apply 10.5 V to pin 1; 4.5 V to pin 24; 3.0 V to pins 23, 19, 18, 8, 7, 6, 4, 3, and 2; and 0.0 V to pins 21, 20, 5, and 12.
- 17/ For unprogrammed device type 02 (circuit G) apply 10.5 V to pins 6 and 1; 4.5 V to pin 24; 3.0 V to pins 23, 19, 18, 8, 7, 4, and 2; 2.0 V to pin 3; 0.0 V to pins 21, 20, 12, and 5.
- 18/ For unprogrammed device type 02 (circuit G) apply 10.5 V to pins 1 and 6; 5.5 V to pin 24; 3.0 V to pins 23, 19, 18, 8, 7, 4, 3 and 2; 0.0 V to pins 5, 12, 20, and 21.
- 19/ For programmed device type 04 (circuit G) apply 10.5 V to pin 16; 4.5 V to pin 20; 3.0 V to pins 1, 2, 3, 4, 5, 18, and 19; 0.0 V to pins 10 and 15.
- 20/ For programmed device type 05 (circuit G) apply 10.5 V to pin 16; 4.5 V to pin 20; 3.0 V to pins 1, 2, 3, 4, 5, 18, and 19; 0.0 V to pins 10 and 15.
- 21/ For unprogrammed device type 05 (circuit G) apply 10.5 V to pins 17 and 3; 4.5 V to pin 20; 3.0 V to pins 2, 4, 5, 16, 18, and 19; 0.0 V to pins 1, 10, and 15.
- 22/ For unprogrammed device type 05 (circuit G) apply 10.5 V to pins 3 and 17; 5.5 V to pin 20; 3.0 V to pins 2, 4, 5, 16, 18, and 19; 0.0 V to pins 1, 10, and 15.
- 23/ At the manufacturer's option, this may be prepared with $V_{IH} = 5.5$ and test limits of 50 μA maximum.
- 24/ At the manufacturer's option, this may be performed with $V_{IO} = 0.5$ V and test limits of -1 μA minimum to -250 μA maximum.
- 25/ For unprogrammed device type 02 (circuit H) apply 5.0V to pin 24; 0.0V to pins 3, 5, 6, 7, 8, 20, and 21; 3.0V to pins 1, 2, 18, 19, and 23; 9.0V to pin 4.

4.4.2 Group B inspection. Group B inspection shall be in accordance with table II MIL-PRF-38535.

4.4.3 Group C inspection. Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:

- a. End-point electrical parameters shall be as specified in table II herein.
- b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- c. For qualification, at least 25 percent of the sample selected for life testing shall be programmed (see 3.3.2). For quality conformance inspection, the programmability sample (see 4.4.1c) shall be included in the life test.

4.4.4 Group D inspection. Group D inspection shall be in accordance with table V of MIL-PRF-38535 and as follows:

- a. End-point electrical tests shall be as specified in table II herein.
- b. Subgroup 2 shall be omitted for devices in package Z.
- c. For moisture resistance and salt atmosphere of subgroups 3 and 5, omit initial conditioning for devices in package Z.

4.5 Methods of inspection. Methods of inspection shall be as specified and as follows:

4.5.1 Voltage and current. All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

4.6 Programming procedure identification. The programming procedure to be utilized shall be identified by the manufacturer's circuit designator.

4.7 Programming procedure for circuit A. The waveforms on figure 7a, the programming characteristics in table IVA and the following procedures shall apply:

- a. Connect the device in the electrical configuration for programming.
- b. Address the PROM with the binary address of the selected word to be programmed. Address inputs are TTL compatible.
- c. Disable the chip by applying V_{IH} to the $\overline{CE}_1$ and $\overline{CE}_2$ inputs and V_{IL} to the CE_3 and CE_4 inputs. The CE inputs are TTL compatible.
- d. Disable the programming circuitry by applying a voltage of V_{OPD} to the outputs of the PROM.
- e. Raise V_{CC} to V_{PH} as specified on the waveforms on figure 7a.
- f. After a delay of t_D , apply only one V_{OPE} pulse with duration of t_p to the output selected for programming. Note that the PROM is supplied with fuses generating a high-level logic output. Programming a fuse will cause the output to go to a low-level logic in the verify mode.

- g. Other bits in the same word may be programmed sequentially while the V_{CC} input is at the V_{PH} level by applying V_{OPE} pulses to each output to be programmed allowing a delay of t_D between pulses as shown on figure 7a.
- h. Repeat steps 4.7b through 4.7g for all other bits to be programmed.
- i. Lower V_{CC} to 4.5 volts following a delay of t_D from the last programming pulse applied to an output.
- j. Enable the chip by applying V_{IL} to the $\overline{CE}_1$ and $\overline{CE}_2$ inputs and V_{IH} to the CE_3 and CE_4 inputs and verify the program.
- k. For class S and B devices, if any bit does not verify as programmed, it shall be considered a programming reject.

TABLE IVA. Programming characteristics for circuit A.

Parameter	Symbol	Limits <u>1/</u>			Unit
		Min	Recommended	Max	
Address input voltage <u>2/</u>	V_{IH}	2.4	5.0	5.0	V
	V_{IL}	0.0	0.4	0.8	V
V_{CC} required during programming	V_{PH}	12.0	12.0	12.5	V
	V_{PL}	4.5	4.5	5.5	V
Programming input low current	I_{ILP}	----	-300	-600	μA
Programming voltage transition time	t_{TLH}	1	1	10	μs
	t_{THL}	1	1	10	μs
Programming delay	t_D	10	10	100	μs
Programming pulse width	t_P	90	100	110	μs
Programming duty cycle	D.C.	----	50	90	%
Output voltage Enable <u>3/</u> Disable <u>4/</u>	V_{OPE}	10.5	10.5	11.0	V
	V_{OPD}	4.5	5.0	5.5	V
Output voltage enable current	I_{OPE}	----	----	10	mA

1/ $T_A = +25^\circ C$.2/ Address and chip enable shall not be left open for V_{IH} .3/ V_{OPE} supply shall be capable of sourcing 10 mA.4/ Disable condition can be met with output open circuit.

4.8 Programming procedure for circuit B. The waveforms on figure 7b, the programming characteristics of table IVB, and the following procedures shall apply:

- a. Connect the device in the electrical configuration for programming.
- b. Raise V_{CC} to 5.5 volts.
- c. Address the PROM with the binary address of the selected word to be programmed. Address inputs are TTL compatible.
- d. Disable the chip by applying V_{IH} to the $\overline{CE}_1$ and $\overline{CE}_2$ and V_{IL} to the CE_3 and CE_4 inputs (device types 01 and 02) or V_{IH} to the CE input (device types 04 and 05). The CE input is TTL compatible.
- e. Apply the V_{PP} pulse to the programming pin $\overline{CE}_2$ (device types 01 and 02) or $\overline{CE}$ (device types 04 and 05). In order to insure that the output transistor is off before increasing the voltage on the output pin, the programming pin's voltage pulse shall precede the output pin's programming pulse by T_{D1} and leave after the output pin's programming pulse by T_{D2} (see figure 7b).
- f. Apply only one V_{OUT} pulse with duration of t_p to the output selected for programming. The outputs shall be programmed one output at a time, since internal decoding circuitry is capable of sinking only one unit of programming current at a time. Note that the PROM is supplied with fuses generating a high-level logic output. Programming a fuse will cause the output to go to a low-level logic in the verify mode.
- g. Other bits in the same word may be programmed sequentially by applying V_{PP} pulses to each output to be programmed.
- h. Repeat 4.8c through 4.8g for all other bits to be programmed.
- i. Enable the chip by applying V_{IL} to the $\overline{CE}_1$ and $\overline{CE}_2$ and V_{IH} to the CE_3 and CE_4 inputs (device types 01 and 02) or V_{IL} to the $\overline{CE}$ inputs (device types 04 and 05) and verify the program. Verification may check for a low output by requiring the device to sink 12 mA at $V_{CC} = 4.0$ V and 0.2 mA at $V_{CC} = 7.0$ V at $T_A = 25^\circ\text{C}$.
- j. For class S and B devices, if any bit does not verify as programmed, it shall be considered a programming reject.

TABLE IVB. Programming characteristics for circuit B.

Parameter	Symbol	Conditions	Limits <u>1/</u>			Unit
			Min	Recommended	Max	
V _{CC} required during programming	V _{CCP}		5.4	5.5	5.6	V
Rise time of programming pulse to data out or programming pin	t _{TLH}		0.34	0.40	0.46	V/μs
Programming voltage on programming pin	V _{PP}		32.5	33	33.5	V
Output programming voltage	V _{OUT}		25.6	26	26.5	V
Programming pin pulse width (CE ₂) <u>2/</u>	t _{PP}	Chip disabled, V _{CC} = 5.5 V		100	180	ns
Pulse width of programming voltage	t _P	Chip disabled, V _{CC} = 5.5 V	1		40	μs
Required current limit of power supply feeding programming pin and output during programming	I _L	V _{PP} = 33 V, V _{OUT} = 26 V, V _{CC} = 5.5 V	240			mA
Required time delay between disabling memory output and application of output programming pulse	T _{D1}	Measured at 10% levels	70	80	90	μs
Required time delay between removal of programming pulse and enabling memory output	T _{D2}	Measured at 10% levels	100			ns
Output current during verification	I _{OLV1}	Chip enabled, V _{CC} = 4.0 V	11	12	13	mA
	I _{OLV2}	Chip enabled, V _{CC} = 7.0 V	0.19	0.2	0.21	mA
Address input voltage	V _{IH}		2.4	5.0	5.5	V
	V _{IL}		0.0	0.4	0.8	V
Maximum duty cycle during automatic programming of program pin and output pin	D.C.	t _P / t _C	----	----	25	%

1/ T_A = +25°C.2/ CE₁ is the programming pin for device types 04 and 05.

4.9 Programming procedures for circuits C and H. The waveforms on figure 7c, the programming characteristics in table IVC, and the following procedures shall be used for programming the device:

4.9.1 Device types 01 and 02.

- a. Connect the device in the electrical configuration for programming.
- b. Terminate all device outputs with a 10 k Ω resistor to V_{CC} . Apply $\overline{CE}_1 = V_{IH}$, $\overline{CE}_2 = V_{IL}$, $CE_3 = V_{IH}$, and $CE_4 = V_{IH}$.
- c. Address the PROM with the binary address of the selected word to be programmed. Raise V_{CC} to V_{CCP} .
- d. After a t_D delay (10 μ s), apply only one V_{OUT} pulse to the output to be programmed. Program one output at a time.
- e. After a t_D delay (10 μ s), pulse CE_1 input to logic "0" for a duration of t_P .
- f. After a t_D delay (10 μ s), remove the V_{OUT} pulse from the programmed output. Programming a fuse will cause the output to go to a high-level logic in the verify mode.
- g. Other bits in the same word may be programmed sequentially while the V_{CC} input is at the V_{CCP} level by applying V_{OUT} pulses to each output to be programmed allowing a delay of t_D between pulses as shown on figure 7c.
- h. Repeat 4.9.1c through 4.9.1g for all other bits to be programmed.
- i. To verify programming, after t_D (10 μ s) delay, lower V_{CC} to V_{CCH} and apply a logic "0" level to both $\overline{CE}_1$ and $\overline{CE}_2$ inputs. The programmed output should remain in the "1" state. Again, lower V_{CC} to V_{CCL} and verify that the programmed output remains in the "1" state.
- j. For class S and B devices, if any bit does not verify as programmed it shall be considered a programming reject.

4.9.2 Device type 03.

- a. Connect the device in the electrical configuration for programming.
- b. Terminate all device outputs with a 10 k Ω resistor to V_{CC} . Apply $\overline{CE}_1 = V_{IL}$, $\overline{CE}_2 = V_{IH}$, and $\text{strobe} = V_{IH}$.
- c. Address the PROM with the binary address of the selected word to be programmed. Raise V_{CC} to V_{CCP} .
- d. After a t_D delay (10 μ s), apply to FE_1 (pin 13) a voltage source of $+5.0 \pm 0.5$ V, with 10 mA sourcing current capability.
- e. After a t_D delay (10 μ s), apply only one V_{OUT} pulse to the output to be programmed. Program one output at a time.
- f. After a t_D delay (10 μ s), raise FE_2 (pin 11) from GND to $+5.0 \pm 0.5$ V for 1 ms, and return to GND.
- g. After a t_D delay (10 μ s), remove the V_{OUT} pulse from the programmed output.

- h. Programming a fuse will cause the output to go to a high level logic in the verify mode. Other bits in the same word may be programmed sequentially while the V_{CC} input is at the V_{CCP} level by applying V_{OUT} pulses to each output to be programmed allowing a delay to t_D between pulses as shown on figure 7c.
- i. Repeat 4.9.2c through 4.9.2h for all other bits to be programmed.
- j. To verify programming after a t_D (10 μ s) delay, return FE_1 to GND. Raise V_{CC} to V_{CCH} . The programmed output should remain in the high state. Again lower V_{CC} to V_{CCL} and verify that the programmed output remains in the high state.
- k. For class S and B devices, if any bit does not verify as programmed it shall be considered a programming reject.

TABLE IVC. Programming characteristics for circuits C and H.

Parameter	Symbol	Conditions	Limits			Unit
			Min	Recommended	Max	
Programming voltage to V_{CC}	V_{CCP} <u>1/</u>	$I_{CCP} = 375 \pm 75$ mA Transient or steady-state	8.5	8.75	9.0	V
Verification upper limit	V_{CCH}		5.3	5.5	5.7	V
Verification lower limit	V_{CCL}		4.3	4.5	4.7	V
Verify threshold	V_S <u>2/</u>		1.4	1.5	1.6	V
Programming supply current	I_{CCP}	$V_{CCP} = 8.75 \pm 0.25$ V	300		450	mA
Input voltage, high level "1"	V_{IH}		2.4		5.5	V
Input voltage, low level "0"	V_{IL}		0	0.4	0.8	V
Input current	I_{IH}	$V_{IH} = 5.5$ V			50	μ A
Input current	I_{IL}	$V_{IL} = 0.4$ V			-500	μ A
Output programming voltage	V_{OUT} <u>3/</u>	$I_{OUT} = 200 \pm 20$ mA Transient or steady-state	16	17	18	V
Output programming current	I_{OUT}	$V_{OUT} = 17 \pm 1$ V	180	200	220	mA
Programming voltage transition time	t_{TLH}		10		50	μ s
$\overline{CE}$ programming pulse width	t_P		300	400	500	μ s
Pulse sequence delay	t_D		10			μ s

1/ Bypass V_{CC} to GND with a 0.01 μ F capacitor to reduce voltage spikes.

2/ V_S is the sensing threshold of the PROM output voltage for a programmed bit. It normally constitutes the reference voltage applied to a comparator circuit to verify a successful fusing attempt.

3/ Care should be taken to insure the 17 ± 1 V output voltage is maintained during the entire fusing cycle. The recommended supply is a constant current source clamped at the specified voltage limit.

4.10 Programming procedure for circuit D. The waveforms on figure 7d, the programming characteristics of table IVD, and the following procedures shall apply:

- a. Connect the device in the electrical configuration for programming.
- b. Address the PROM with the binary address of the selected word to be programmed. Address inputs are TTL compatible.
- c. Disable the chip by applying V_{IH} to the $\overline{CE}_1$ and $\overline{CE}_2$ inputs and V_{IL} to the CE_3 and CE_4 inputs. The chip enable input is TTL compatible.
- d. After a delay of t_D , apply only one V_{OUT} pulse with a duration of t_p to the output selected for programming. The other outputs may be left open or tied to V_{IH} . The outputs shall be programmed one output at a time. Note that the PROM is supplied with fuses generating a high-level logic output. Programming a fuse will cause the output to go to a low-level logic in the verify mode.
- e. Other bits in the same word may be programmed sequentially by applying V_{OUT} pulses to each output to be programmed.
- f. Repeat 4.10b through 4.10e for all other bits to be programmed.
- g. Enable the chip by applying V_{IL} to the $\overline{CE}_1$ and $\overline{CE}_2$ inputs and V_{IH} to the CE_3 and CE_4 inputs and verify the program.
- h. For class S and B devices, if any bit does not verify as programmed, it shall be considered a programming reject.

TABLE IVD. Programming characteristics for circuit D.

Parameter	Symbol	Conditions <u>1/</u>	Limits			Unit
			Min	Recommended	Max	
V _{CC} required during programming	V _{CCP}		4.75	5.0	5.25	V
Verification V _{CC} read	V _{CCL}	Programming read verify	4.2	4.4	5.0	V
Input voltage, high level "1"	V _{IH}	Do not leave inputs open	2.4	5.0	5.0	V
Input voltage, low level "0"	V _{IL}	Do not leave inputs open	0	0	0.4	V
Output programming voltage	V _{OUT}	Applied to output to be programmed	20	20.5	21	V
Output programming current	I _{OUT}	If pulse generator is used, set current limit to the max value			100	mA
Programming voltage transition time	t _{TLH}		0.5	1.0	3.0	μs
Programming pulse width	t _P		50	100	180	μs
Programming duty cycle	D. C.	Maximum duty cycle to maintain T _A < +85°C		20	20	%
Required delay between disabling memory output and application of output programming pulse	t _D		30			ns

1/ Recommended T_A = +25°C; maximum T_A = +85°C.

4.11 Programming procedure for circuit F. The waveforms on figure 7f, the programming characteristics on table IVF, and the following procedures shall apply:

- Connect the device in the electrical configuration for programming.
- Raise V_{CC} to 5.5 Volts.
- Address the PROM with the binary address of the selected word to be programmed. Address inputs are TTL compatible.
- Disable the chip by applying V_{IH} to the $\overline{\text{CE}}$ inputs and V_{IL} to the CE inputs. The chip enable inputs are TTL compatible.
- Apply the V_{PP} pulse to the programming pin $\overline{\text{CE}}_2$. In order to insure that the output transistor is off before increasing voltage on the output pin, the programming pin's voltage pulse shall precede the output pin's programming pulse by TD₁ and leave after the programming pin's programming pulse by TD₂ (see figure 7f).
- Apply only one V_{OUT} pulse with duration of t_P to the output selected for programming. The outputs shall be programmed one output at a time, since internal decoding circuitry is capable of sinking only one unit of programming current at a time. Note that the PROM is supplied with fuses generating a high-level logic output. Programming a fuse will cause the output to go to a low-level logic in the verify mode.

- g. Other bits in the same word may be programmed sequentially by applying V_{OUT} pulses to each output to be programmed.
- h. Repeat steps 4.11c through 4.11g for all other bits to be programmed.
- i. Enable the chip by applying V_{IL} to the $\overline{CE}$ inputs and V_{IH} to the CE inputs, and verify the program. Verification may check for a low output by requiring the device to sink 12 mA at $V_{CC} = 4.0$ V and 0.2 mA at $V_{CC} = 7.0$ V at $T_A = 25^\circ\text{C}$.
- j. For class S and B devices, if any bit does not verify as programmed, it shall be considered a programming reject.

TABLE IVF. Programming characteristics for circuit F – Continued.

Parameter	Symbol	Conditions	Limits ^{1/}			Unit
			Min	Recommended	Max	
V_{CC} required during programming	V_{CCP}		5.4	5.5	5.6	V
Rise time of programming pulse data out or programming pin	t_{TLH}		0.34	0.40	0.46	V/ μs
Programming voltage on programming pin	V_{PP}		32.5	33	33.5	V
Output programming voltage	V_{OUT}		25.5	26	26.5	V
Programming pin pulse width (CE)	t_{PP}	Chip disabled, $V_{CC} = 5.5$ V		100	180	ns
Pulse width of programming voltage	t_P	Chip disabled, $V_{CC} = 5.5$ V	1		40	μs
Required current limit of power supply feeding programming pin and output during programming	I_L	$V_{PP} = 33$ V, $V_{OUT} = 26$ V, $V_{CC} = 5.5$ V	240			mA
Required time delay between disabling memory output and application of output programming pulse	T_{D1}	Measured at 10% levels	70	80	90	μs
Required time delay between removal of programming pulse and enabling memory output	T_{D2}	Measured at 10% levels	100	----	----	ns
Output current during verification	I_{OLV1}	Chip enabled, $V_{CC} = 4.0$ V	11	12	13	mA
	I_{OLV2}	Chip enabled, $V_{CC} = 7.0$ V	0.19	0.2	0.21	mA
Address input voltage	V_{IH}		2.4	5.0	5.5	V
	V_{IL}		0.0	0.4	0.8	V
Maximum duty cycle during automatic programming of program pin and output pin	D. C.	t_P / t_C	----	----	25	%

^{1/} $T_A = +25^\circ\text{C}$.

4.12 Programming procedure for circuit G. The programming characteristics on table IVG and the following procedures shall be used for programming:

- a. Connect the device in the electrical configuration for programming. The waveforms on figure 7g and the programming characteristics of table IVG shall apply to these procedures.
- b. Select the desired word by applying high or low levels to the appropriate address inputs. Disable the device by applying a high level to one or more 'active low' chip Enable inputs. NOTE: Address and enable inputs must be driven with TTL logic levels during programming and verification.
- c. Increase V_{CC} from nominal to V_{CCP} (10.5 ± 0.5 V) with a slew rate limit of I_{RR} (1.0 to 10.0 V/ μ s). Since V_{CC} is the source of the current required to program the fuse as well as the I_{CC} for the device at the programming voltage, it must be capable of supplying 750 mA at 11.0 volts.
- d. Select the output where a logical high is desired by raising that output voltage to V_{OP} (10.5 ± 0.5 V). Limit the slew rate to I_{RR} (1.0 to 10.0 V/ μ s). This voltage change may occur simultaneously with the V_{CC} increase to V_{CCP} , but must not precede it. It is critical that only one output at a time be programmed since the internal circuits can only supply programming current to one bit at a time. Outputs not being programmed must be left open or connected to a high impedance source of 20 k Ω minimum (remember that the outputs of the device are disabled at this time).
- e. Enable the device by taking the chip Enable(s) to a low level. This is done with a pulse PWE for 10 μ s. The 10 μ s duration refers to the time that the circuit (device) is enabled. Normal input levels are used and rise and fall times are not critical.
- f. Verify that the bit has been programmed by first removing the programming voltage from the output and then reducing V_{CC} to 5.0 (± 0.25 V). The device must be enabled to sense the state of the outputs. During verification, the loading of the output must be within specified I_{OL} and I_{OH} limits.
- g. If the device is not to be tested for V_{OH} over the entire operating range subsequent to programming, the verification of Step f is to be performed at a V_{CC} level of 4.0 volts (± 0.2 V). V_{OH} , during the 4 volt verification, must be at least 2.0 volts. The 4 volt V_{CC} verification assures minimum V_{OH} levels over the entire operating range.
- h. Repeat steps 4.12b through 4.12f for each bit to be programmed to a high level. If the procedure is performed on an automatic programmer, the duty cycle of V_{CC} at the programming voltage must be limited to a maximum of 25 percent. This is necessary to minimize device junction temperatures. After all selected bits are programmed, the entire contents of the memory should be verified.
- i. For class S and B devices, if any bit does not verify as programmed, it shall be considered a programming reject.

TABLE IVG. Programming characteristics for circuit G.

Parameter	Symbol	Conditions	Limits <u>1/</u>			Unit
			Min	Recommended	Max	
Required V_{CC} during programming	V_{CCP}		10.0	10.5	11.0	V
I_{CC} during programming	I_{CCP}	$V_{CC} = 11\text{ V}$			750	mA
Required output voltage for programming	V_{OP}		10.0	10.5	11.0	V
Output current while programming	I_{OP}	$V_{OUT} = 11\text{ V}$			20	mA
Rate of voltage change of V_{CC} or output	I_{RR}		1.0		10.0	V/ μ s
Programming pulse width (Enabled)	PWE		9	10	11	μ s
Required V_{CC} for verification	V_{CCV}		3.8	4.0	4.2	V
Maximum duty cycle for V_{CC} at V_{CCP}	MDC			25	25	%
Address set-up time	t_1		100			ns
V_{CCP} set-up time	t_2	<u>2/</u>	5			μ s
V_{CCP} hold time	t_5		100			ns
V_{OP} set-up time	t_3		100			ns
V_{OP} hold time	t_4		100			ns

1/ $T_A = +25^\circ\text{C}$.2/ V_{CCP} set-up time may be greater than 0 if V_{CCP} rises at the same rate or faster than V_{OP} .

5. PACKAGING

5.1 Packaging requirements. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Service or Defense Agency, or within the military service's system command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature which may be helpful, but is not mandatory.)

6.1 Intended use. Microcircuits conforming to this specification are intended for logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of the specification.
- b. PIN and compliance identifier, if applicable (see 1.2).
- c. Requirements for delivery of one copy of the conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
- d. Requirements for certificate of compliance, if applicable.
- e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
- f. Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
- g. Requirements for product assurance options.
- h. Requirements for special lead lengths, or lead forming, if applicable. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
- i. Requirement for programming the device, including processing option. The device may be programmed pre- or post-burn-in, if applicable.
- j. Requirements for "JAN" marking.
- k. Packaging Requirements (see 5.1)

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA LAND AND MARITIME-VQ, 3990 E. Broad Street, Columbus, Ohio 43218-3990.

6.4 Superseding information. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential.
V _{IN}	Voltage level at an input terminal
V _{IC}	Input clamp voltage
I _{IN}	Current flowing into an input terminal

6.6 Logistic support. Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish C (see 3.4). Longer length leads and lead forming should not affect the part number. It is intended that spare devices for logistic support be acquired in the unprogrammed condition (see 3.8.1) and programmed by the maintenance activity, except where use quantities for devices with a specific program or pattern justify stocking of preprogrammed devices.

6.7 Substitutability. The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-38510 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device type	Generic-industry Type	Circuit Designator	Fusible Links	Symbol/ FSCM no.
01	7640/Harris Corporation	A	NiCr	CDWO/34371
01	5340-1/Monolithic Memories, Inc.	B	NiCr	CECD/50364
01	82S140/Signetics Corporation	C	NiCr	CDKB/18324
01	82S140/ e2v aerospace & defense, inc.	C	ZVE	0C7V7
01	93438/Fairchild Corporation	D	NiCr	CFJ/07263
01	54S475/National Semiconductor	G	TiW	CCXP/27014
02	7641/Harris Corporation	A	NiCr	----
02	5341-1/Monolithic Memories, Inc.	B	NiCr	----
02	82S141/Signetics Corporation	C	NiCr	----
02	82S141/e2v aerospace & defense, inc.	H	ZVE	0C7V7
02	93448/Fairchild Corporation	D	NiCr	----
02	54S474/National Semiconductor	G	TiW	----
03	82S115/Signetics Corporation	C	NiCr	----
03	82S115/ e2v aerospace & defense, inc.	C	ZVE	0C7V7
04	5348-1/Monolithic Memories, Inc.	B	NiCr	----
04	54S473/National Semiconductor	G	TiW	----
05	5349-1/Monolithic Memories, Inc.	B	NiCr	----
05	29621/Raytheon Company	F	NiCr	CRP/07933
05	54S472/National Semiconductor	G	TiW	----

6.8 Change from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extent of the changes.

Custodians:
 Army - CR
 Navy - EC
 Air Force - 85
 DLA - CC

Preparing activity:
 DLA - CC

Review activities:
 Army – SM, MI
 Navy - AS, CG, MC, SH
 Air Force – 03, 19, 99

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NOTE: The activities listed above were interested in this document as of the date of this document. Since organization and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.